US 20250267993A1

(19) **United States**

(12) **Patent Application Publication**

(10) **Pub. No.: US 2025/0267993 A1**

(43) **Pub. Date: Aug. 21, 2025**

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(54) **DISPLAY DEVICE**

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(21) Appl. No.: **18/894,742**

(22) Filed: **Sep. 24, 2024**

(30) **Foreign Application Priority Data**

Feb. 20, 2024 (KR) 10-2024-0024192

Publication Classification

(51) **Int. Cl.**

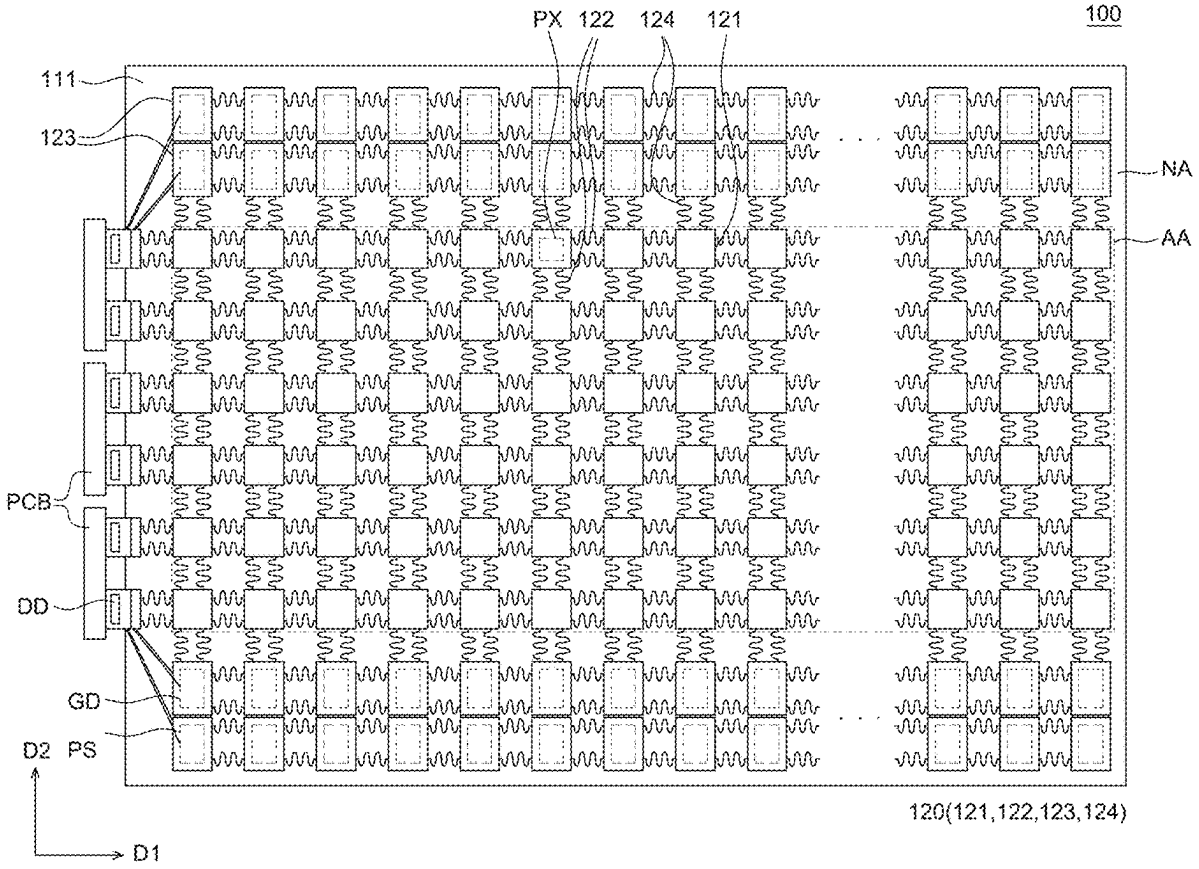
H01L 33/60 (2010.01)
H01L 25/16 (2023.01)
H01L 33/50 (2010.01)

(52) **U.S. Cl.**

CPC ***H10H 20/856*** (2025.01); ***H01L 25/167*** (2013.01); ***H10H 20/8515*** (2025.01)

(57) **ABSTRACT**

A display device in one example includes a lower substrate having a plurality of rigid areas disposed to be spaced apart from each other and a malleable area enclosing the plurality of rigid areas, a plurality of first plate patterns disposed in the plurality of rigid areas of the lower substrate, and a plurality of first sub pixels partially disposed on the plurality of first plate patterns. Each of the plurality of first sub pixels includes a first light emitting diode, a light conversion layer facing one side surface of the first light emitting diode, and a first reflective layer facing an opposite surface of one side surface of the first light emitting diode.



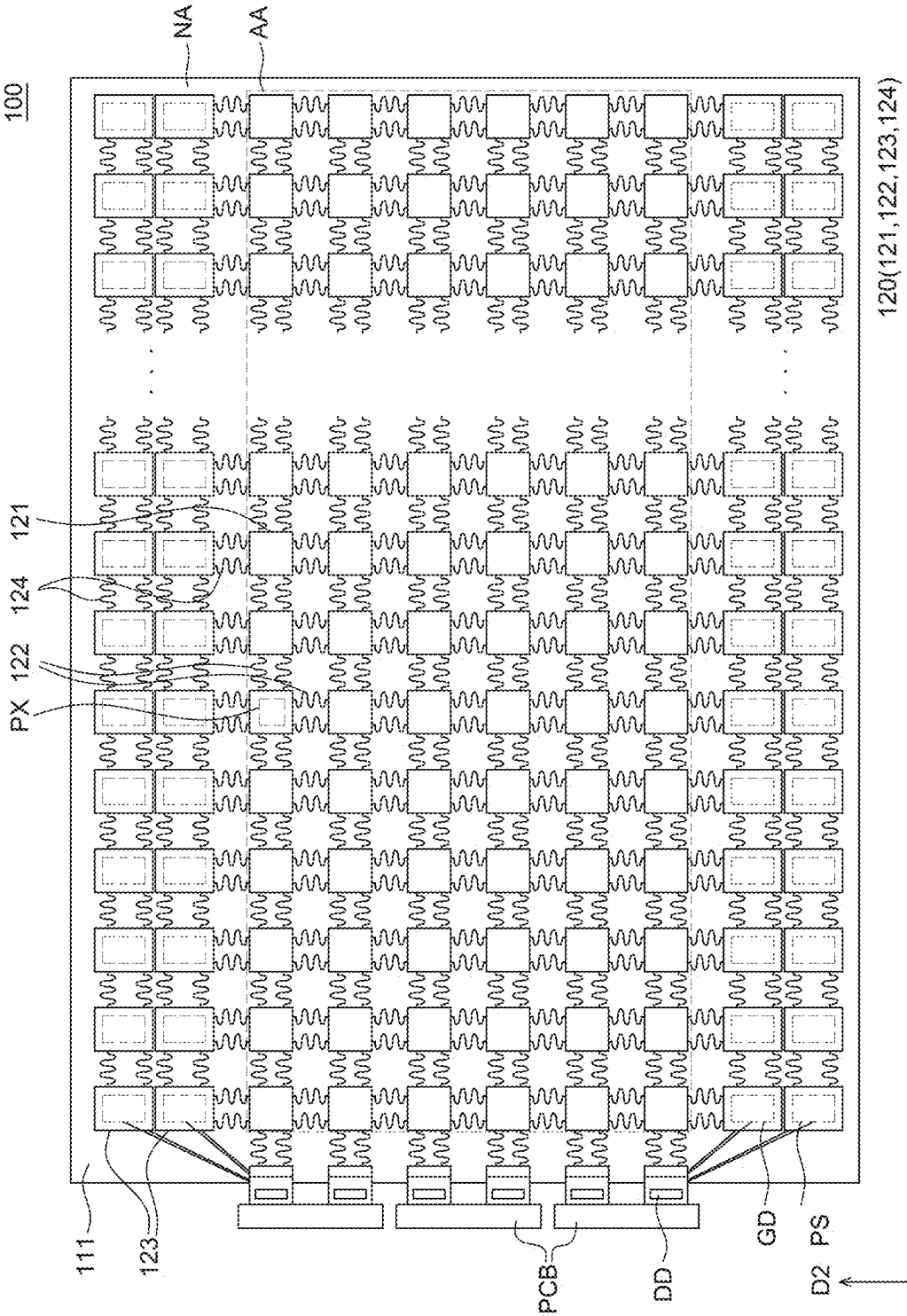

100
NA
AA
120(121,122,123,124)
121
124
122
PX
111
123
PCB
DD
GD
PS
D1
D2

FIG. 1

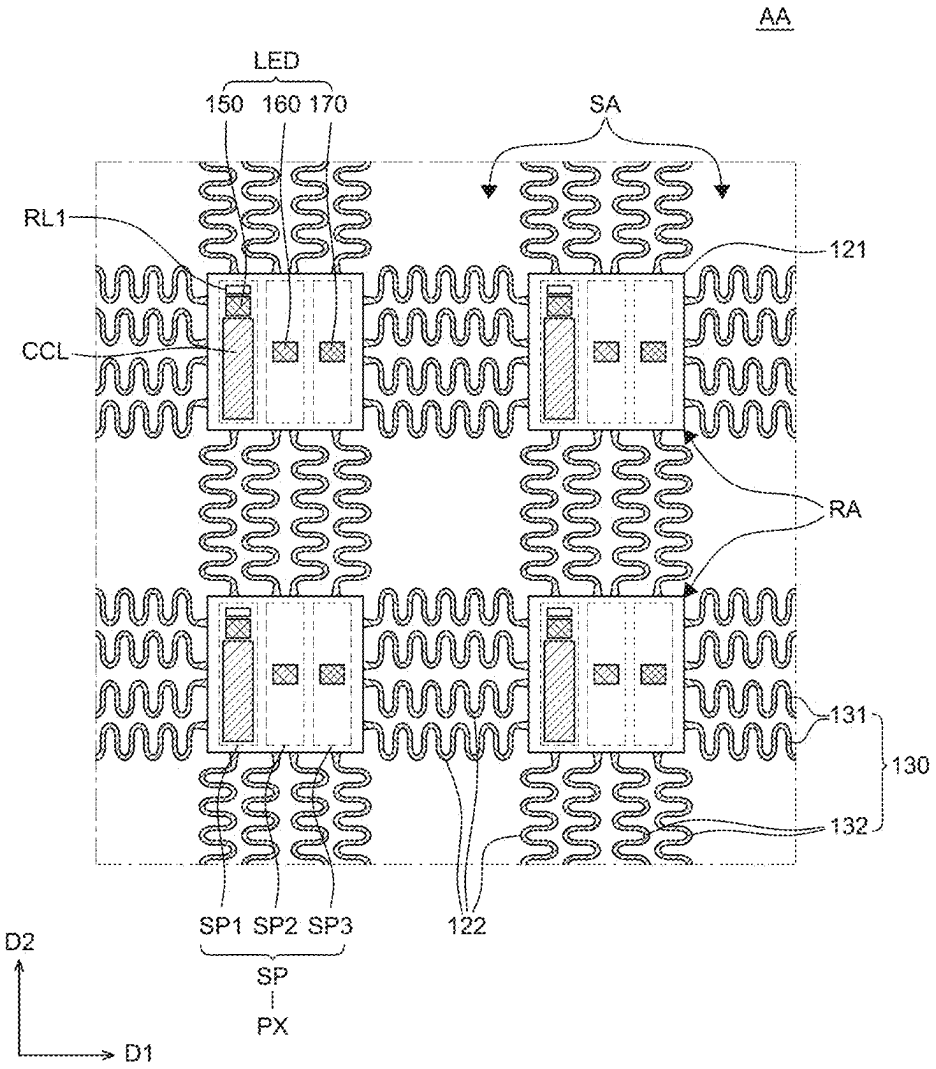
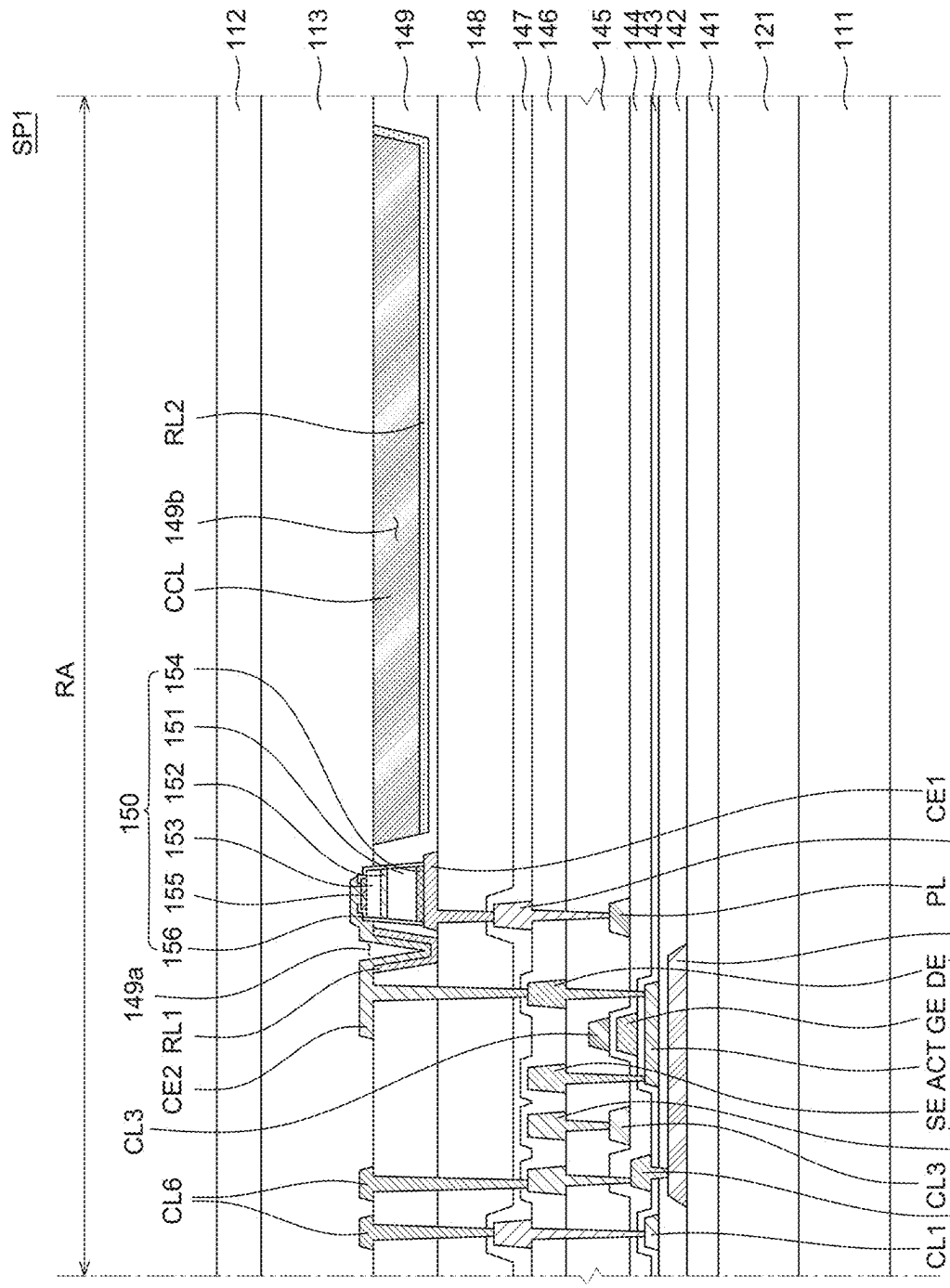

AA
LED
150 160 170
SA
RL1
121
CCL
RA
131
130
132
SP1 SP2 SP3
122
SP
PX
D2
D1

FIG. 2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141
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111
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149b
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152
153
150
155
156
149a
RL1
CE2
CL3
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CL5
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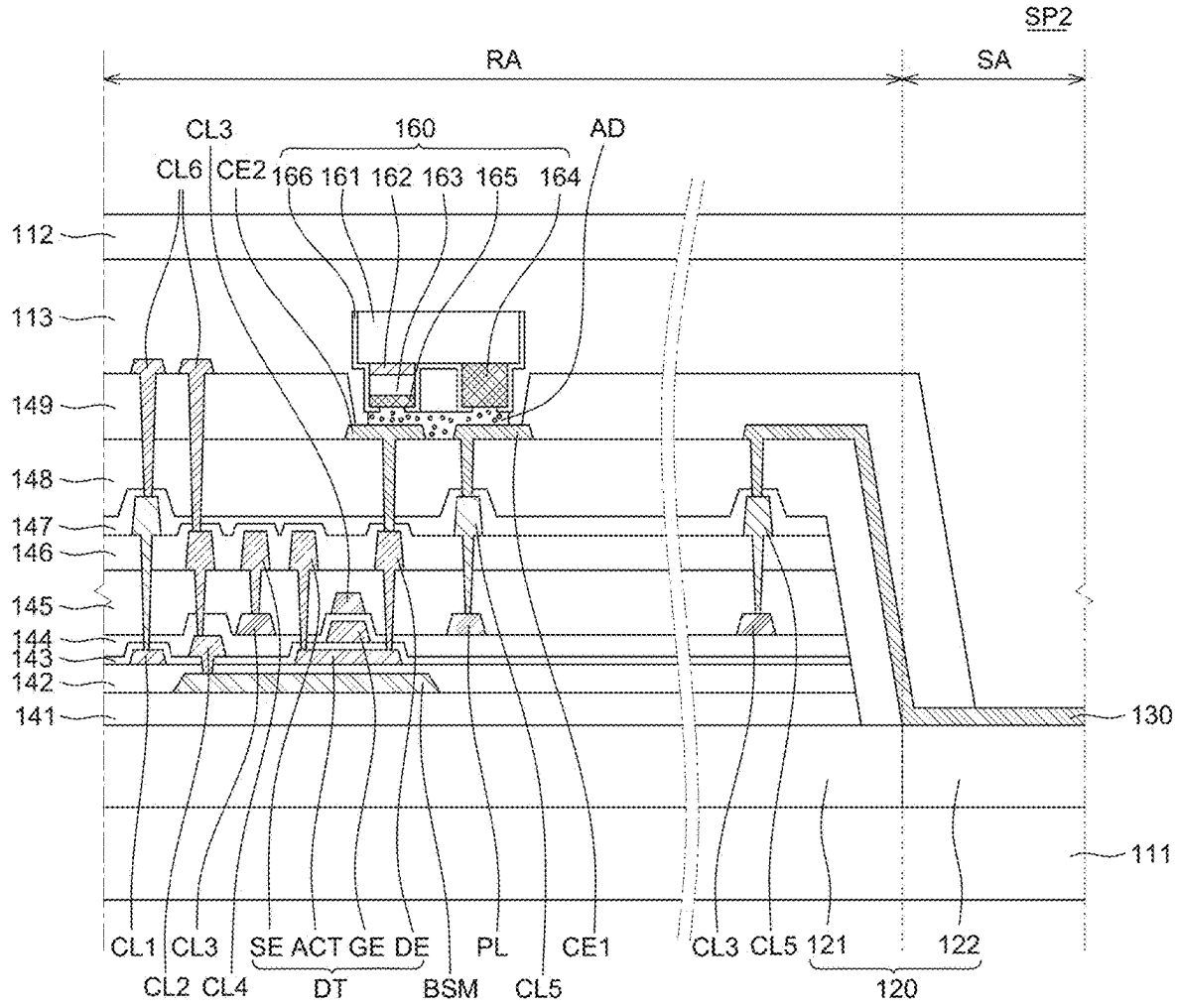
ACT
SE
DT
CL3
CL4
CL2
CL1

FIG. 3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160
AD
CL6
CE2
166 161 162 163 165 164
112
113
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148
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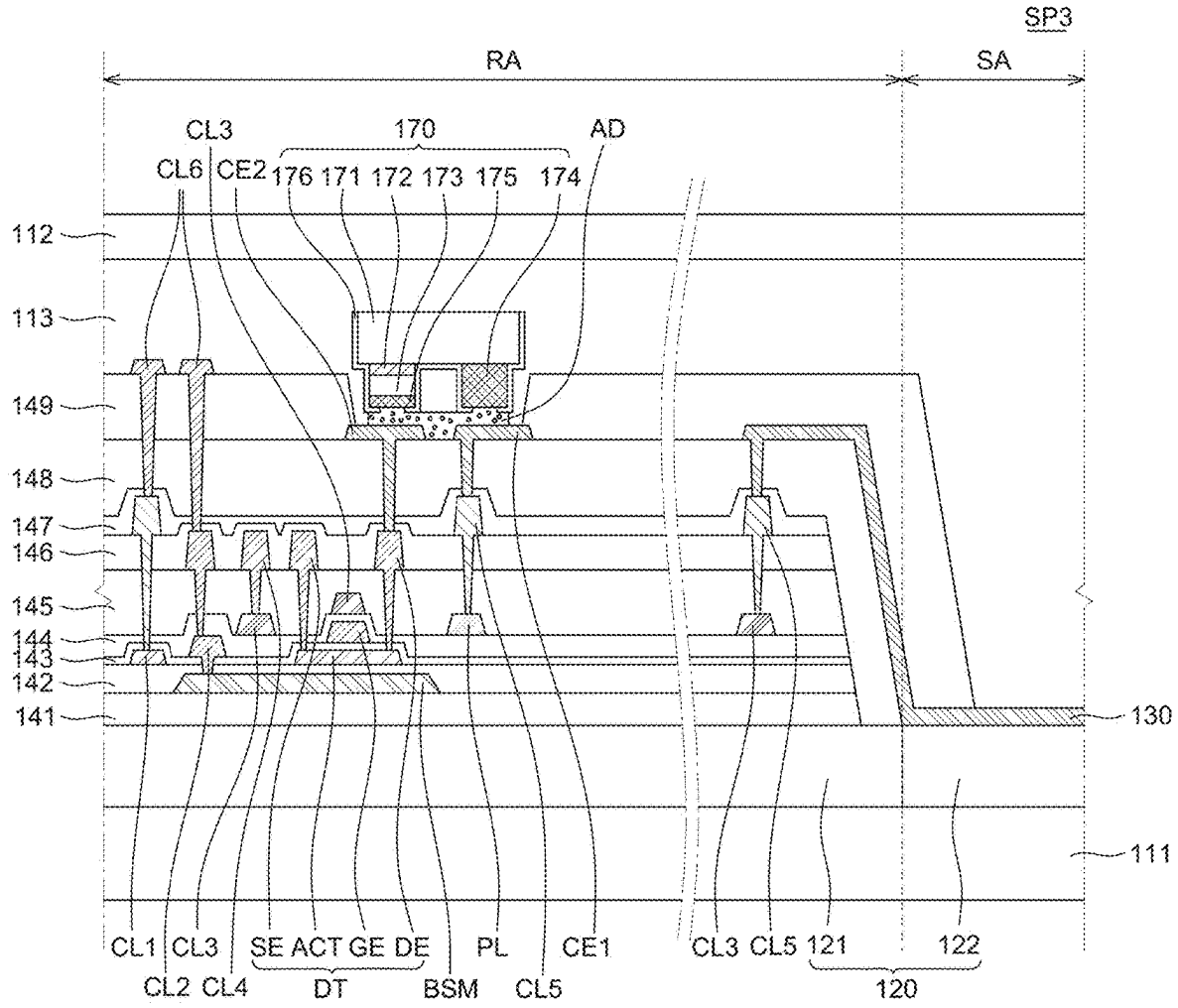
142
141
130
111
CL1
CL3
SE ACT GE DE
PL
CE1
CL3 CL5 121
122
CL2 CL4
DT
BSM
CL5
120

FIG. 4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AD
CL6
CE2
176 171 172 173 175 174
112
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142
141
130
111
CL1
CL3
SE ACT GE DE
PL
CE1
CL3 CL5
121
122
CL2 CL4
DT
BSM
CL5
120

FIG. 5

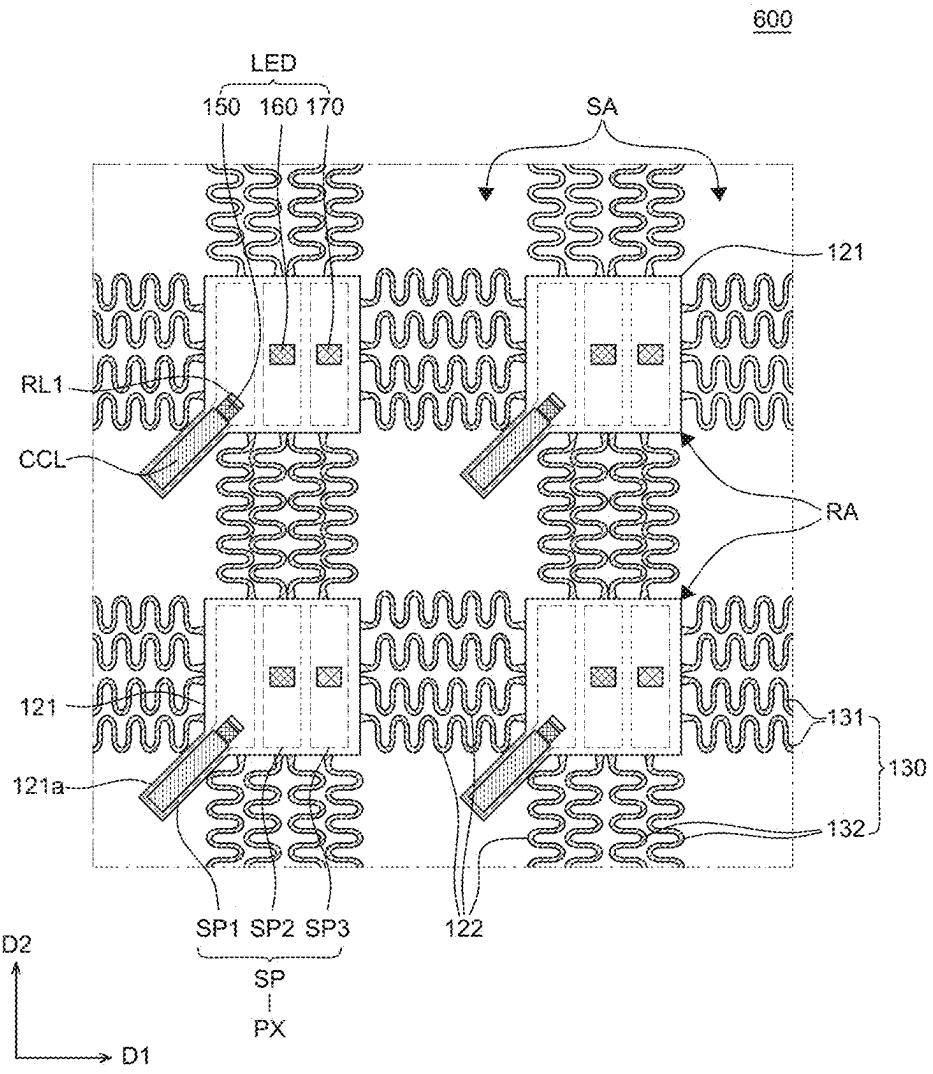

600
LED
150 160 170
SA
121
RL1
CCL
RA
121
131
130
121a
132
SP1 SP2 SP3
122
SP
PX
D2
D1

FIG. 6

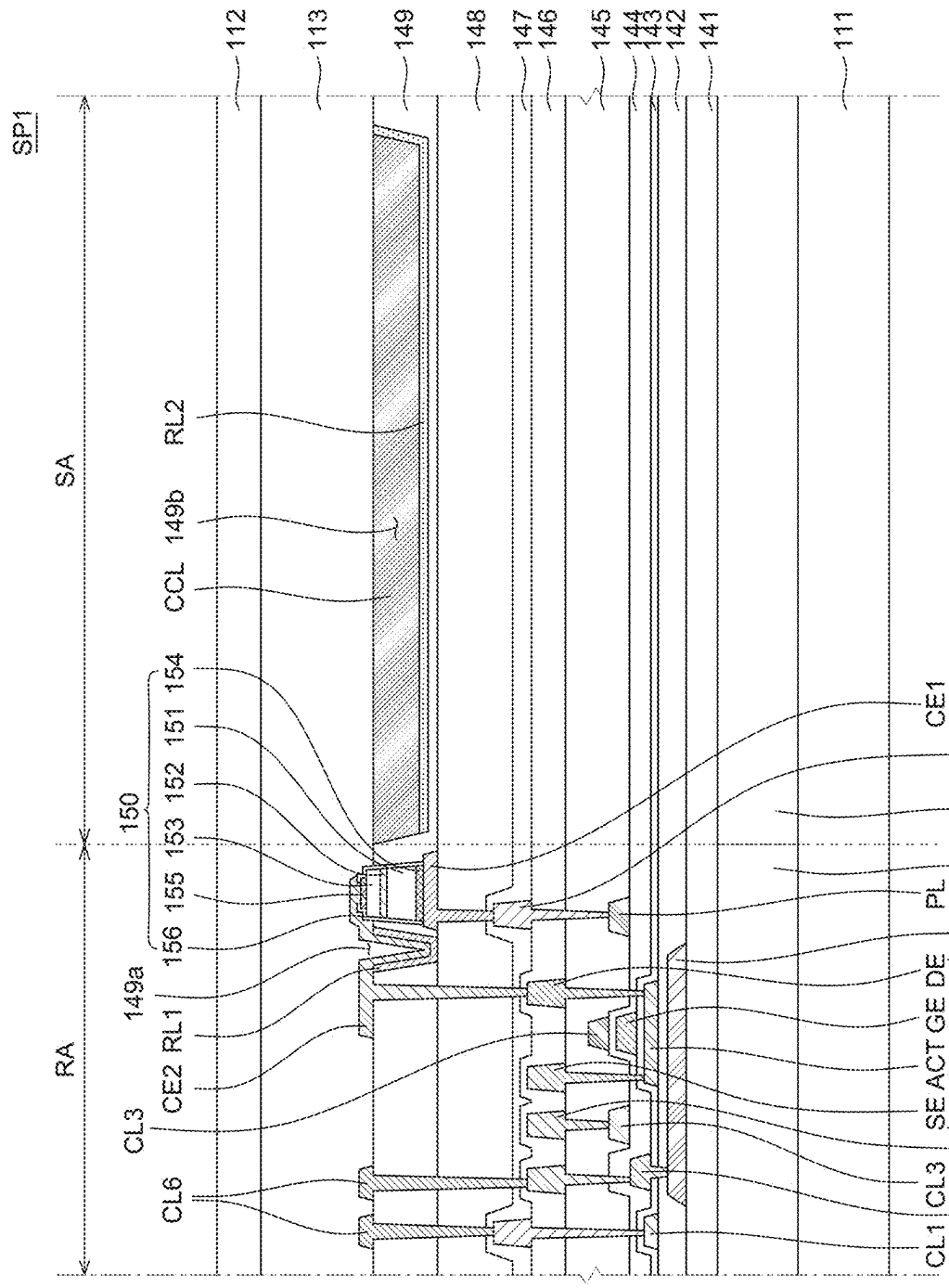

SP1
SA
RA
112
113
149
148
147
146
145
144
143
142
141
111
RL2
149b
CCL
154
151
152
153
150
155
156
149a
RL1
CE2
CL3
CL6
CE1
CL5
121a
121
PL
BSM
DE
GE
ACT
SE
DT
CL3
CL4
CL2
CL1

FIG. 7

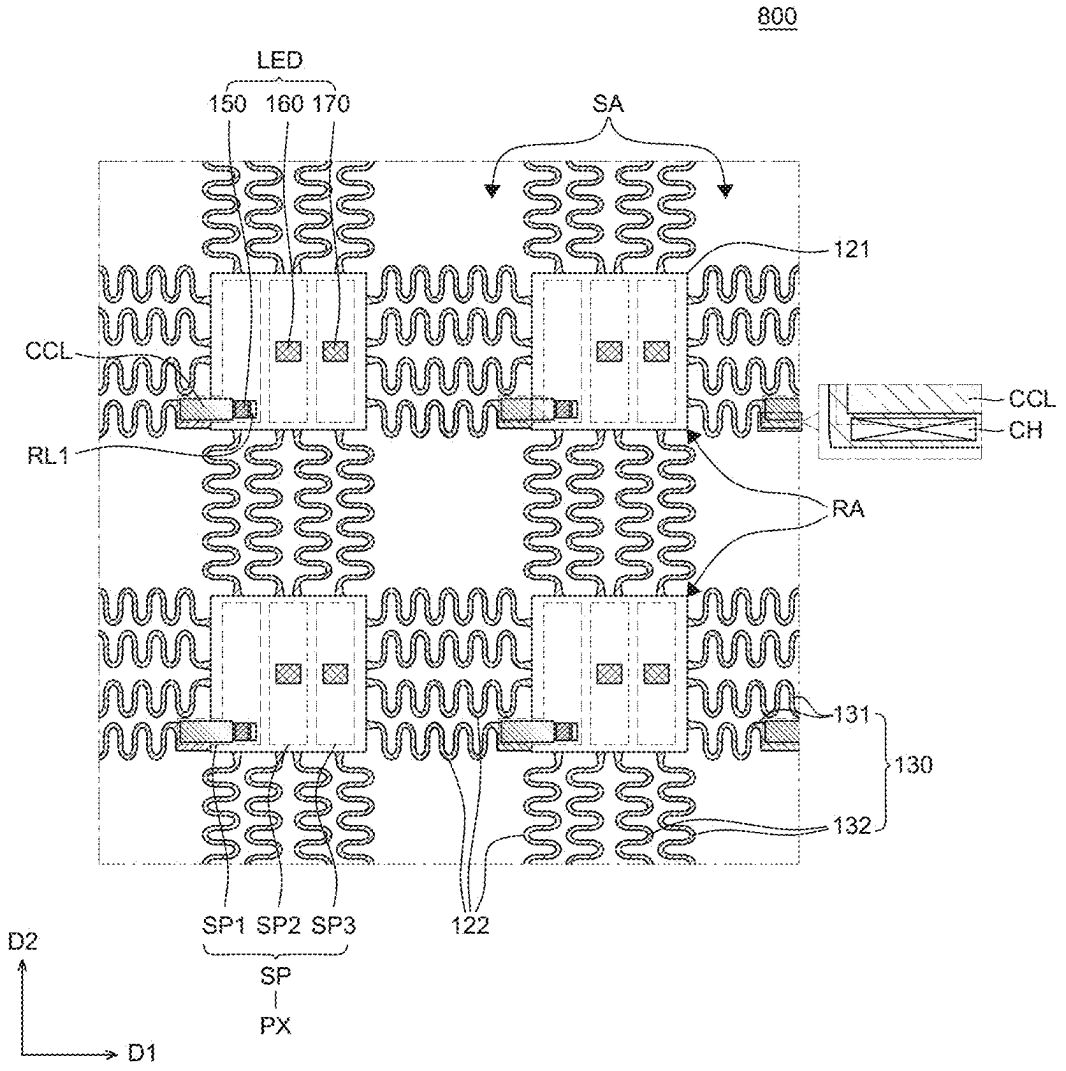
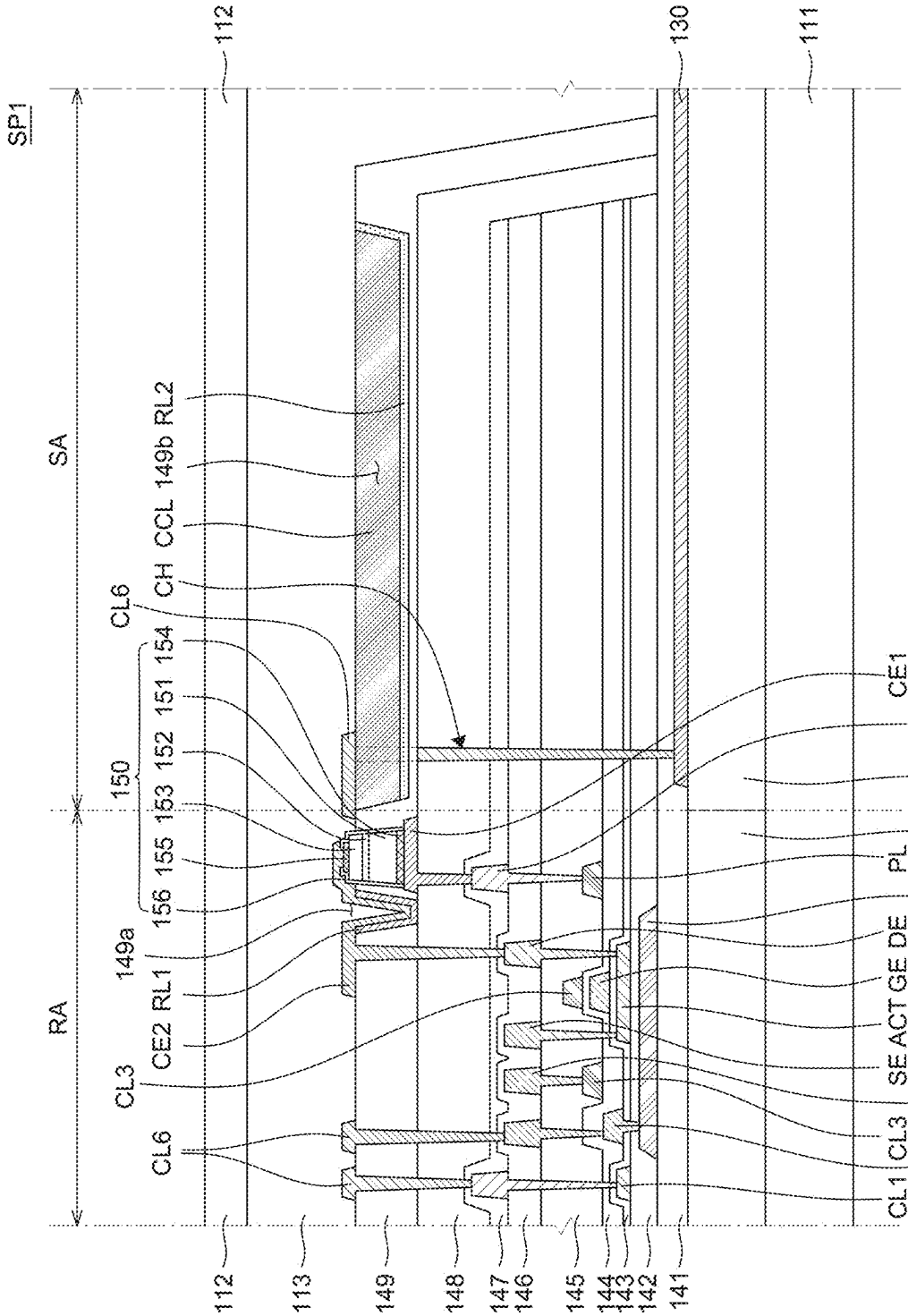

800
LED
150 160 170
SA
121
CCL
CCL
CH
RL1
RA
131
130
132
SP1 SP2 SP3
122
SP
PX
D2
D1

FIG. 8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CCL
CH
CL6
154
151
152
153
155
156
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149a
RL1
CE2
CL3
CL6
CE1
CL5
122
120
121
PL
BSM
DE
GE
ACT
SE
DT
CL1
CL3
CL2
CL4
112
113
149
148
147
146
145
144
143
142
141

FIG. 9

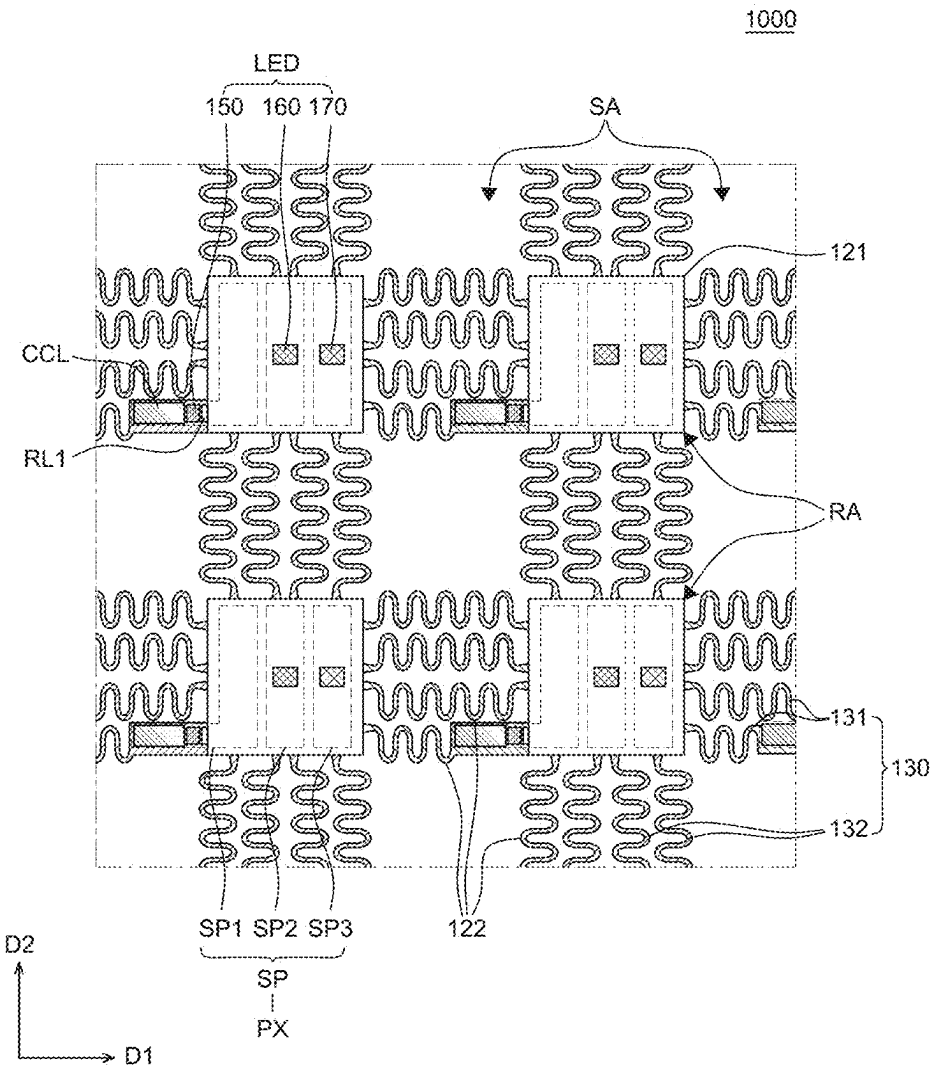
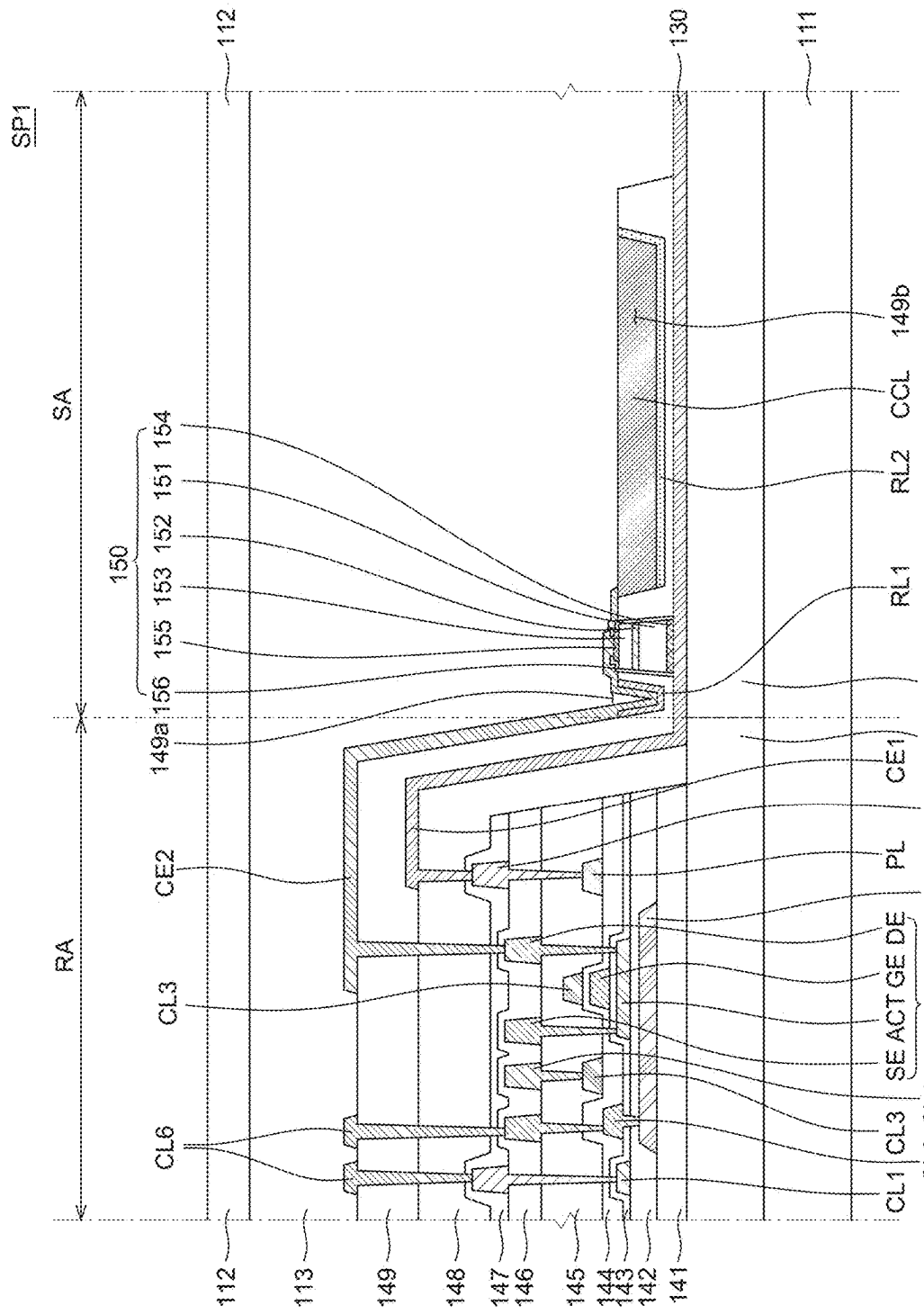

1000
LED
150 160 170
SA
121
CCL
RL1
RA
131
130
132
SP1 SP2 SP3
122
SP
PX
D2
D1

FIG. 10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111
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CCL
RL2
RL1
122
120
121
CE1
CL5
PL
BSM
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ACT
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CL4
CL3
CL2
CL1
CL6
CE2
CL3
150
154
151
152
153
155
156
149a
112
113
149
148
147
146
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143
142
141

FIG. 11

DISPLAY DEVICE

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application claims priority to Korean Patent Application No. 10-2024-0024192 filed on Feb. 20, 2024, in the Korean Intellectual Property Office, the entire contents of which is hereby expressly incorporated by reference into the present application.

BACKGROUND

Field

[0002] The present disclosure relates to a display device, and more particularly to a stretchable display device which can be stretched.

Discussion of the Related Art

[0003] Display devices can be used for a monitor of a computer, a television, or a cellular phone. Among such display devices, there are an organic light emitting display device (OLED) which is a self-emitting device, a liquid crystal display device (LCD) which requires a separate light source, and the like.

[0004] An applicable range of the display device is diversified to personal digital assistants as well as monitors of computers and televisions. A display device with a large display area and a reduced volume and weight is being studied.

[0005] Further, a display device is manufactured by forming a display unit, a wiring line, and the like on a flexible substrate made of a flexible material such as plastic. This renders the display device to be stretchable in a specific direction and changed in various forms, which is getting attention as a next generation display device.

SUMMARY OF THE DISCLOSURE

[0006] An object to be achieved by the present disclosure is to provide a display device with an improved efficiency of red light.

[0007] Another object to be achieved by the present disclosure is to provide a display device with an improved light conversion efficiency of a red light conversion layer.

[0008] Still another object to be achieved by the present disclosure is to provide a display device which improves a light conversion efficiency by forming a light conversion layer to have a long length.

[0009] Still another object to be achieved by the present disclosure is to provide a display device in which a light emitting diode and a light conversion layer are formed together in a rigid area.

[0010] Still another object to be achieved by the present disclosure is to provide a display device in which a light emitting diode is formed in a rigid area and a light conversion layer is formed in a malleable area.

[0011] Still another object to be achieved by the present disclosure is to provide a display device in which a light conversion layer is formed on a connection line.

[0012] Still another object to be achieved by the present disclosure is to provide a display device in which a light emitting diode and a light conversion layer are formed together on a connection line.

[0013] Still another object to be achieved by the present disclosure is to provide a display device in which a step between a light conversion layer of a malleable area and a light emitting diode of a rigid area is minimized.

[0014] Objects of the present disclosure are not limited to the above-mentioned objects, and other objects, which are not mentioned above, can be clearly understood by those skilled in the art from the following descriptions.

[0015] According to an aspect of the present disclosure, a display device includes a lower substrate having a plurality of rigid areas disposed to be spaced apart from each other and a malleable area enclosing the plurality of rigid areas; a plurality of first plate patterns disposed in the plurality of rigid areas of the lower substrate; and a plurality of first sub pixels partially disposed on the plurality of first plate patterns, wherein each of the plurality of first sub pixels includes: a first light emitting diode, a light conversion layer disposed opposite to one side surface of the first light emitting diode, and a first reflective layer disposed opposite to an opposite surface of one side surface of the first light emitting diode. Accordingly, light from the first light emitting diode is reflected to the light conversion layer disposed on a side portion of the first light emitting diode using the first reflective layer to improve a light conversion efficiency of the light conversion layer.

[0016] Other detailed matters of the example embodiments are included in the detailed description and the drawings.

[0017] A display device according to one or more aspects of the present disclosure can improve an efficiency of red light.

[0018] A display device according to one or more aspects of the present disclosure can improve a light conversion efficiency of a red light conversion layer.

[0019] A display device according to one or more aspects of the present disclosure can improve a light conversion efficiency by forming a light conversion layer to have a long length, instead of a thickness of the light conversion layer.

[0020] A display device according to one or more aspects of the present disclosure can form a light emitting diode and a light conversion layer together in a rigid area.

[0021] A display device according to one or more aspects of the present disclosure can form a light emitting diode in a rigid area and a light conversion layer in a malleable area.

[0022] A display device according to one or more aspects of the present disclosure can form a light conversion layer on a connection line.

[0023] A display device according to one or more aspects of the present disclosure can form a light emitting diode and a light conversion layer together on a connection line.

[0024] A display device according to one or more aspects of the present disclosure can minimize a step between a light emitting diode of a malleable area and a light conversion layer in a rigid area.

[0025] The effects according to the present disclosure are not limited to the contents exemplified above, and more various effects are included in the present disclosure.

BRIEF DESCRIPTION OF THE DRAWINGS

[0026] The above and other aspects, features and other advantages of the present disclosure will be more clearly understood from the following detailed description taken in conjunction with the accompanying drawings, in which:

[0027] FIG. **1** is a plan view of a display device according to an example embodiment of the present disclosure;

[0028] FIG. **2** is an enlarged plan view of an active area of a display device according to an example embodiment of the present disclosure;

[0029] FIG. **3** is a cross-sectional view of a first sub pixel of a display device according to an example embodiment of the present disclosure;

[0030] FIG. **4** is a cross-sectional view of a second sub pixel of a display device according to an example embodiment of the present disclosure;

[0031] FIG. **5** is a cross-sectional view of a third sub pixel of a display device according to an example embodiment of the present disclosure;

[0032] FIG. **6** is an enlarged plan view of an active area of a display device according to another example embodiment of the present disclosure;

[0033] FIG. **7** is a cross-sectional view of a first sub pixel of a display device according to another example embodiment of the present disclosure;

[0034] FIG. **8** is an enlarged plan view of an active area of a display device according to still another example embodiment of the present disclosure;

[0035] FIG. **9** is a cross-sectional view of a first sub pixel of a display device according to still another example embodiment of the present disclosure;

[0036] FIG. **10** is an enlarged plan view of an active area of a display device according to still another example embodiment of the present disclosure; and

[0037] FIG. **11** is a cross-sectional view of a first sub pixel of a display device according to still another example embodiment of the present disclosure.

DETAILED DESCRIPTION OF THE EMBODIMENTS

[0038] Advantages and characteristics of the present disclosure and a method of achieving the advantages and characteristics will be clear by referring to example embodiments described below in detail together with the accompanying drawings. However, the present disclosure is not limited to the example embodiments disclosed herein but will be implemented in various forms. The example embodiments are provided by way of example only so that those skilled in the art can fully understand the disclosures of the present disclosure and the scope of the present disclosure.

[0039] The shapes, sizes, ratios, angles, numbers, and the like illustrated in the accompanying drawings for describing the example embodiments of the present disclosure are merely examples, and the present disclosure is not limited thereto. Like reference numerals generally denote like elements throughout the disclosure. Further, in the following description of the present disclosure, a detailed explanation of known related technologies can be omitted to avoid unnecessarily obscuring the subject matter of the present disclosure. The terms such as "including," "having," and "consist of" used herein are generally intended to allow other components to be added unless the terms are used with the term "only". Any references to singular can include plural unless expressly stated otherwise.

[0040] Components are interpreted to include an ordinary error range even if not expressly stated.

[0041] When the position relation between two parts is described using the terms such as "on", "above", "below", and "next", one or more parts can be positioned between the two parts unless the terms are used with the term "immediately" or "directly".

[0042] When an element or layer is disposed "on" another element or layer, one or more additional different layers or elements can be interposed directly on the other element or therebetween.

[0043] Although the terms "first", "second", and the like are used for describing various components, these components are not confined by these terms. These terms are merely used for distinguishing one component from the other components and may not define order or sequence. Therefore, a first component to be mentioned below can be a second component in a technical concept of the present disclosure.

[0044] Like reference numerals generally denote like elements throughout the disclosure.

[0045] A size and a thickness of each component illustrated in the drawing are illustrated for convenience of description, and the present disclosure is not limited to the size and the thickness of the component illustrated. Further, the term "can" fully encompasses all the meanings and coverages of the term "may."

[0046] The features of various embodiments of the present disclosure can be partially or entirely adhered to or combined with each other and can be interlocked and operated in technically various ways, and the embodiments can be carried out independently of or in association with each other.

[0047] Hereinafter, example embodiments of the present disclosure will be described in detail with reference to accompanying drawings. All the components of each display device according to all embodiments of the present disclosure are operatively coupled and configured.

[0048] FIG. **1** is a plan view of a display device according to an example embodiment of the present disclosure. FIG. **2** is an enlarged plan view of an active area of a display device according to an example embodiment of the present disclosure. FIG. **3** is a cross-sectional view of a first sub pixel of a display device according to an example embodiment of the present disclosure. FIG. **4** is a cross-sectional view of a second sub pixel of a display device according to an example embodiment of the present disclosure. FIG. **5** is a cross-sectional view of a third sub pixel of a display device according to an example embodiment of the present disclosure. In FIG. **2**, for the convenience of description, among configurations of a plurality of sub pixels disposed on a first plate pattern **121**, a first reflection layer RL**1**, a light emitting diode LED, and a light conversion layer CCL are illustrated.

[0049] First, a display device **100** according to an example embodiment of the present disclosure is a display device **100** which is capable of displaying images even in a bent or extended state and can also be referred to as a stretchable display device **100**, a flexible display device **100**, and an extendable display device **100**. As compared with the general display devices of the related art, the display device **100** can have not only a high flexibility, but also stretchability. Therefore, the user can bend or extend a display device **100** and a shape of a display device **100** can be freely changed in accordance with manipulation of a user. For example, when the user pulls the display device **100** by holding ends of the display device, the display device **100** can be extended to the pulling direction of the user. Alternatively, when the user disposes the display device **100** on an outer surface

which is not flat, the display device **100** can be disposed to be bent in accordance with the shape of the outer surface. Further, when a force applied by the user is removed, the display device **100** can return to its original shape.

[0050] Referring to FIGS. **1** to **4** together, the lower substrate **111** is a substrate which supports and protects several components of the display device **100**. The lower substrate **111** can support a pattern layer **120** on which the pixels PX, the gate driver GD, and the power supply PS are formed.

[0051] An upper substrate **112** is a substrate which covers and protects several components of the display device **100**. The upper substrate **112** can cover the pixels PX, the gate driver GD, and the power supply PS.

[0052] The lower substrate **111** and the upper substrate **112** which are flexible substrates can be configured by an insulating material which is bendable or extendable. For example, the lower substrate **111** and the upper substrate **112** can be formed of a silicon rubber such as polydimethylsiloxane (PDMS) or an elastomer such as polyurethane (PU) and polytetrafluoroethylene (PTFE) and thus have a flexibility. Further, the materials of the lower substrate **111** and the upper substrate **112** can be the same, but are not limited thereto and can vary.

[0053] The lower substrate **111** and the upper substrate **112** are flexible substrates so as to be reversibly expandable and contractible. Accordingly, the lower substrate **111** can be referred to as a lower stretchable substrate, a lower stretching substrate, a lower extending substrate, a lower ductile substrate, a lower flexible substrate, a first stretchable substrate, a first stretching substrate, a first extending substrate, a first ductile substrate, a first flexible substrate, or the like. The upper substrate **112** can be referred to as an upper stretchable substrate, an upper stretching substrate, an upper extending substrate, an upper ductile substrate, an upper flexible substrate, a second stretchable substrate, a second stretching substrate, a second extending substrate, a second ductile substrate, a second flexible substrate, or the like.

[0054] Moduli of elasticity of the lower substrate **111** and the upper substrate **112** can be several MPa to several hundreds of MPa. Further, a ductile breaking rate of the lower substrate **111** and the upper substrate **112** can be 100% or higher. Here, the ductile breaking rate refers to a stretching rate at a timing when an object to be stretched is broken or cracked. A thickness of the lower substrate **111** can be 10 μm to 1 mm, but is not limited thereto.

[0055] The lower substrate **111** includes an active area AA and a non-active area NA enclosing the active area AA. However, the active area AA and the non-active area NA are not mentioned to be limited to the lower substrate **111**, but mentioned for the entire display device **100**.

[0056] The active area AA is an area in which images are displayed in the display device **100** and a plurality of pixels PX is disposed in the active area AA. Further, each pixel PX can include a display element and various driving elements for driving the display element. Various driving elements can refer to at least one thin film transistor (TFT) and a capacitor, but are not limited thereto. The plurality of pixels PX can be connected to various wiring lines to be driven, respectively. For example, each of the plurality of pixels PX can be connected to various wiring lines, such as a scan line, a data line, a high potential voltage line, a low potential voltage line, a reference voltage line, and an initialization voltage line.

[0057] The non-active area NA is an area where no image is displayed. The non-active area NA can be an area adjacent to the active area AA. Further, the non-active area NA can be adjacent to the active area AA to enclose the active area AA. However, it is not limited thereto so that the non-active area NA corresponds to an area excluding the active area AA from the lower substrate **111** and can be modified and separated in various forms. In the non-active area NA, components for driving a plurality of pixels PX disposed in the active area AA, such as a gate driver GD and a power supply PS, can be disposed. Further, in the non-active area NA, a plurality of pads connected to the data driver DD and the printed circuit board PCB can be disposed and each pad can be connected to each of the plurality of pixels PX of the active area AA.

[0058] A filling layer **113** is disposed between the lower substrate **111** and the upper substrate **112**. The filling layer **113** can be fully filled in an empty space between the lower substrate **111** and the upper substrate **112**. For example, the filling layer **113** can be configured by a curable adhesive. Specifically, the material which configures the filling layer **113** is coated on the entire surface of the lower substrate **111** and then is cured so that the filling layer **113** can be disposed between the components disposed on the upper substrate **112** and the lower substrate **111**. For example, the filling layer **113** can be an optically clear adhesive (OCA) and can be configured by an acrylic-based adhesive, a silicon-based adhesive, and a urethane-based adhesive.

[0059] The pattern layer **120** is disposed on the lower substrate **111**. The pattern layer **120** includes a plurality of first plate patterns **121** and a plurality of first line patterns **122** disposed in the active area AA and a plurality of second plate patterns **123** and a plurality of second line patterns **124** disposed in the non-active area NA.

[0060] A plurality of plate patterns is disposed in the active area AA and the non-active area NA. The plurality of plate patterns includes a plurality of first plate patterns **121** and a plurality of second plate patterns **123**. The plurality of first plate patterns **121** is disposed in the active area AA of the lower substrate **111** and the plurality of second plate patterns **123** is disposed in the non-active area NA of the lower substrate **111**. On the plurality of first plate patterns **121**, a plurality of pixels PX is formed and on the plurality of second plate patterns **123**, a gate driver GD and a power supply PS can be formed.

[0061] The plurality of first plate patterns **121** and the plurality of second plate patterns **123** can be disposed in the form of separate islands. The plurality of first plate patterns **121** and the plurality of second plate patterns **123** can be individually separated. Therefore, the plurality of first plate patterns **121** and the plurality of second plate patterns **123** can be referred to as first island patterns and second island patterns or first individual patterns and second individual patterns.

[0062] A size of each of the plurality of second plate patterns **123** can be larger than a size of each of the plurality of first plate patterns **121**. In each of the plurality of second plate patterns **123**, one stage of the gate driver GD can be disposed. Therefore, an area occupied by various circuit configurations which configure one stage of the gate driver GD can be relatively larger than an area occupied by one pixel PX so that a size of each of the plurality of second plate patterns **123** can be larger than a size of each of the plurality of first plate patterns **121**.

[0063] In the meantime, even though it is illustrated in FIG. **1** that the plurality of second plate patterns **123** is disposed in the non-active area NA on both sides of the active area AA in the second direction D**2**, this is illustrative so that the plurality of second plate patterns **123** can be disposed in an arbitrary area of the non-active area NA. Further, even though it is illustrated that the plurality of first plate patterns **121** and the plurality of second plate patterns **123** have a rectangular shape, it is not limited thereto and the shapes of the plurality of first plate patterns **121** and the plurality of second plate patterns **123** can vary in various forms.

[0064] Referring to FIGS. **1** and **2**, the plurality of line patterns is disposed in the active area AA and the non-active area NA. The plurality of line patterns includes a plurality of first line patterns **122** and a plurality of second line patterns **124**.

[0065] The plurality of first line patterns **122** is disposed in the active area AA. The plurality of first line patterns **122** is patterns which connect first plate patterns **121** which are adjacent to each other and can be referred to as internal connection patterns. For example, the plurality of first line patterns **122** can be disposed between the plurality of first plate patterns **121**.

[0066] The plurality of second line patterns **124** of the pattern layer **120** is disposed in the non-active area NA. The plurality of second line patterns **124** connects the first plate pattern **121** and the second plate pattern **123** which are adjacent to each other or connects a plurality of adjacent second plate patterns **123** and can be referred to as external connection patterns. The plurality of second line patterns **124** can be disposed between the first plate pattern **121** and the second plate pattern **123** which are adjacent to each other and between the plurality of second plate patterns **123** which is adjacent to each other.

[0067] The plurality of first line patterns **122** and the plurality of second line patterns **124** have a wavy shape. For example, the plurality of first line patterns **122** and the plurality of second line patterns **124** can have a sinusoidal shape. However, the shape of the plurality of first line patterns **122** and the plurality of second line patterns **124** is not limited thereto. For example, the plurality of first line patterns **122** and the plurality of second line patterns **124** can extend in a zigzag pattern. Further, the plurality of first line patterns **122** and the plurality of second line patterns **124** can have various shapes such as a shape in which a plurality of rhombic substrates is connected at their vertexes to be extended or a shape in which semi-circular and quadrant-shaped substrates are connected to each other. Further, the number and the shape of the plurality of first line patterns **122** and the plurality of second line patterns **124** illustrated in FIG. **1** are illustrative and can be changed in various forms depending on the design.

[0068] In the meantime, the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** are rigid patterns. For example, the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be more rigid than the lower substrate **111** and the upper substrate **112**.

[0069] The plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** which are rigid substrates can be formed of a plastic material having a lower flexibility than the lower substrate **111** and the upper substrate **112**. For example, the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be formed of at least one material of polyimide (PI), polyacrylate, and polyacetate. At this time, when the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** are formed of the same material, the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** are integrally formed. However, when the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be formed of different materials, but are not limited thereto.

[0070] Moduli of elasticity of the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be higher than a modulus of elasticity of the lower substrate **111**. The modulus of elasticity is a parameter representing a rate of deformation against the stress applied to the substrate and the higher the modulus of elasticity, the higher the hardness. Therefore, the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be referred to as a plurality of first rigid patterns, a plurality of second rigid patterns, a plurality of third rigid patterns, and a plurality of fourth rigid patterns, respectively. Moduli of elasticity of the plurality of first plate patterns **121**, the plurality of first line patterns **122**, the plurality of second plate patterns **123**, and the plurality of second line patterns **124** can be 1000 times or higher than the moduli of elasticity of the lower substrate **111** and the upper substrate **112**, but it is not limited thereto.

[0071] In the meantime, in some example embodiments, the lower substrate **111** can be defined to include a plurality of rigid areas RA and malleable areas SA. The plurality of rigid areas RA can be disposed to be spaced apart from each other. The plurality of rigid areas RA can be areas of the lower substrate **111** overlapping the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. The plurality of rigid areas RA can be areas in which the plurality of first plate patterns **121** and the plurality of second plate patterns **123** are disposed to have a rigid characteristic. The malleable area SA can be an area which encloses each of the plurality of rigid areas RA. The malleable area SA can be an area which does not overlap the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. The malleable area SA is an area between the plurality of first plate patterns **121** and the plurality of second plate patterns **123** and can include an area in which the plurality of first line patterns **122** and the plurality of second line patterns **124** are disposed. Further, the malleable area SA can include an area in which the pattern layer **120** is not disposed. The malleable area SA can be an area in which the plurality of first plate patterns **121** and the plurality of second plate patterns **123** are not disposed to be flexibly deformable. In the plurality of rigid areas RA, the plurality of first plate patterns **121** and the plurality of second plate patterns **123** are disposed. In the malleable area SA, the plurality of first plate patterns **121**

and the plurality of second plate patterns **123** are not disposed. Therefore, the plurality of rigid areas RA can be more rigid than the malleable area SA. At this time, the malleable area SA and the plurality of rigid areas RA are not mentioned to be limited to the lower substrate **111**, but mentioned for the entire display device **100**.

[0072] Further, in some example embodiments, the lower substrate **111** can be defined to include a plurality of first lower patterns and a second lower pattern. The plurality of first lower patterns can be an area of the lower substrate **111** overlapping the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. The second lower pattern can be a remaining area which does not overlap the plurality of first plate patterns **121** and the plurality of second plate patterns **123**.

[0073] Furthermore, the upper substrate **112** can be defined to include a plurality of first upper patterns and a second upper pattern. The plurality of first upper patterns can be an area overlapping the plurality of the first plate patterns **121** and the plurality of second plate patterns **123** of the upper substrate **112**, but the second upper pattern can be a remaining area which does not overlap the plurality of the first plate patterns **121** and the plurality of second plate patterns **123**.

[0074] At this time, moduli of elasticity of the plurality of first lower patterns and the first upper pattern can be higher than moduli of elasticity of the second lower pattern and the second upper pattern. For example, the plurality of first lower patterns and the first upper pattern can be formed of the same material as the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. The second lower pattern and the second upper pattern can be formed of a material having a modulus of elasticity lower than those of the plurality of first plate patterns **121** and the plurality of second plate patterns **123**.

[0075] For example, the first lower pattern and the first upper pattern can be formed of polyimide (PI), polyacrylate, polyacetate, or the like. Further, the second lower pattern and the second upper pattern can be formed of silicon rubber such as polydimethylsiloxane (PDMS) or elastomer such as polyurethane (PU) or polytetrafluoroethylene.

[0076] The gate driver GD can be mounted on the plurality of second plate patterns **123**. The gate driver GD can be formed on the plurality of second plate patterns **123** in a gate in panel (GIP) manner when various elements on the plurality of first plate patterns **121** are manufactured. Therefore, various circuit configurations which configure the gate driver GD, such as transistors, capacitors, and wiring lines, can be disposed on the plurality of second plate patterns **123**. One stage which is a circuit which configures the gate driver GD and includes transistors and capacitors can be disposed above each of the plurality of second plate patterns **123**. However, the gate driver GD can be mounted in a chip on film (COF) manner, but is not limited thereto.

[0077] A power supply PS can be disposed on the plurality of second plate patterns **123**. The power supply PS can be formed on the second plate pattern **123** adjacent to the gate driver GD. The power supply PS is a plurality of power blocks patterned when various components on the first plate pattern **121** is manufactured and can be formed on the second plate pattern **123**. The power supply PS is electrically connected to the gate driver GD of the non-active area NA and the plurality of pixels PX of the active area AA to supply a driving voltage. Specifically, the power supply PS can be electrically connected to the gate driver GD formed on the second plate pattern **123** and the plurality of pixels PX formed on the first plate pattern **121** by means of the second line pattern **124** and the first line pattern **122**. For example, the power supply PS can supply a gate driving voltage and a clock signal to the gate driver GD. Further, the power supply PS can supply the power voltage to each of the plurality of pixels PX.

[0078] The printed circuit board PCB is connected to an edge of the lower substrate **111**. The printed circuit board PCB is a component which transmits signals and voltages for driving the display element from the control unit to the display element. Therefore, the printed circuit board PCB can also be referred to as a driving substrate. A controller, such as an IC chip or a circuit unit, can be mounted on the printed circuit board PCB. Further, on the printed circuit board PCB, a memory, a processor, or the like, can also be mounted. Further, the printed circuit board PCB provided in the display device **100** can include a stretching area and a non-stretching area to ensure stretchability. Further, in the non-stretching area, an IC chip, a circuit unit, a memory, a processor, and the like can be mounted. In the stretching area, wiring lines which are electrically connected to the IC chip, the circuit unit, the memory, and the processor can be disposed.

[0079] The data driver DD is a component which supplies a data voltage to the plurality of pixels PX disposed in the active area AA. The data driver DD is configured as an IC chip so that it can be also referred to as a data integrated circuit D-IC. Further, the data driver DD can be mounted in the non-stretching area of the printed circuit board PCB. For example, the data driver DD can be mounted on the printed circuit board PCB in the form of a chip on board (COB). However, even though in FIG. **1**, it is illustrated that the data driver DD is mounted in a COB manner, the data driver DD can be mounted in a chip on film (COF), a chip on glass (COG), or a tape carrier package (TCP) manner, but it is not limited thereto.

[0080] Further, even though in FIG. **1**, one data driver DD is disposed so as to correspond to each of a plurality of columns formed by the plurality of first plate patterns **121** disposed in the active area AA, it is not limited thereto. For example, one data driver DD can be disposed so as to correspond to a plurality of columns formed by a plurality of first plate patterns **121**.

[0081] Referring to FIGS. **1** and **2**, the plurality of first plate patterns **121** is disposed in the active area AA of the lower substrate **111**. The plurality of first plate patterns **121** can be disposed to be spaced apart from each other. For example, the plurality of first plate patterns **121** can be disposed in a plurality of rows and a plurality of columns to be disposed in a matrix. For example, the plurality of first plate patterns **121** is disposed to be spaced apart from each other with a predetermined interval in the first direction D**1**. The plurality of first plate patterns **121** can be disposed to be spaced apart from each other with a predetermined interval in the second direction D**2**.

[0082] The plurality of first line patterns **122** can be disposed in the active area AA of the lower substrate **111**. The plurality of first line patterns **122** is disposed in an area between the plurality of first plate patterns **121** to connect the plurality of first plate patterns **121**. The plurality of first line patterns **122** extends in the first direction D**1** or the second direction D**2** and can connect the first plate patterns

121 which are adjacent to each other in the first direction D1 or the second direction D2. For example, some first line patterns extending in the first direction D1, among the plurality of first line patterns 122, can connect one pair of first plate patterns 121 which are adjacent to each other in the first direction D1. The remaining first line patterns 122 extending in the second direction D2, among the plurality of first line patterns 122, can connect one pair of first plate patterns 121 which are adjacent to each other in the second direction D2.

[0083] In the meantime, an adhesive layer can be further disposed between the pattern layer 120 and the lower substrate 111. The adhesive layer is a layer for bonding the lower substrate 111 and the pattern layer 120. When the display device 100 is formed, after sequentially forming configurations of the pattern layer 120 and the plurality of sub pixels SP on a rigid substrate, the rigid substrate and the pattern layer 120 are separated and the lower substrate 111 can be attached below the pattern layer 120. At this time, in order to fix the pattern layer 120 and the lower substrate 111, the adhesive layer can be disposed between the pattern layer 120 and the lower substrate 111. For example, the adhesive layer can be an optically clear adhesive (OCA), but is not limited thereto.

[0084] Next, a pixel PX including the plurality of sub pixels SP which is an individual unit to emit light is disposed in the plurality of first plate patterns 121. The plurality of sub pixels SP can form one pixel PX. N sub pixels SP which form one pixel PX can be disposed in each of the plurality of first plate patterns 121. The plurality of sub pixels SP can include a first sub pixel SP1, a second sub pixel SP2, and a third sub pixel SP3. The first sub pixel SP1 is a red sub pixel SP, a second sub pixel SP2 is a green sub pixel SP, and a third sub pixel SP3 can be a blue sub pixel SP.

[0085] In the meantime, it is illustrated that one pixel PX includes three sub pixels SP. However, as a variation, the plurality of sub pixels SP can further include a white sub pixel depending on a design of the display device and the number and a configuration of the plurality of sub pixels SP which forms one pixel PX are not limited thereto.

[0086] Each of the plurality of sub pixels SP includes a light emitting diode LED which is a display element and a pixel circuit for driving the light emitting diode LED.

[0087] The light emitting diode LED can be configured by any one of various elements depending on a type of the display device 100. For example, when the display device 100 is an organic light emitting display device, the light emitting diode LED can be an organic light emitting diode and when the display device 100 is an inorganic light emitting display device, the light emitting diode LED can be a light emitting diode LED or a micro LED. Hereinafter, it is assumed that the light emitting diode LED is a micro LED, but it is not limited thereto.

[0088] The pixel circuit supplies the driving current to the light emitting diode LED to allow the light emitting diode LED to emit light. The pixel circuit can include a plurality of transistors and capacitors. For example, the pixel circuit can include a plurality of transistors, such as a driving transistor DT or a switching transistor and a capacitor which is connected to any one of the plurality of transistors.

[0089] Hereinafter, the plurality of sub pixels SP of the display device according to aspects of the present disclosure will now be described in more detail with reference to FIGS. 2 to 5.

[0090] Referring to FIGS. 2 to 5, a plurality of inorganic insulating layers is disposed on the plurality of first plate patterns 121. For example, the plurality of inorganic insulating layers can include a multi-buffer layer 141, an active buffer layer 142, a gate insulating layer 143, a first interlayer insulating layer 144, a second interlayer insulating layer 145, a third interlayer insulating layer 146, and a passivation layer 147. However, in addition to the above-described inorganic insulating layers, another inorganic insulating layer can be additionally disposed or one or more of the above-described inorganic insulating layers can be omitted. A configuration of the plurality of inorganic insulating layers is not limited thereto.

[0091] First, the multi-buffer layer 141 is disposed on the plurality of first plate patterns 121 and the active buffer layer 142 is disposed on the multi-buffer layer 141. The multi-buffer layer 141 and the active buffer layer 142 reduce the permeation of moisture or impurities from the outside of the lower substrate 111 and the first plate pattern 121. The multi-buffer layer 141 and the active buffer layer 142 can protect various components of the display device 100 from the moisture and oxygen of the outside. The multi-buffer layer 141 and the active buffer layer 142 can be formed of an insulating material. For example, the multi-buffer layer 141 and the active buffer layer 142 are configured by a single layer or a double layer of silicon nitride (SiNx), silicon oxide (SiOx), and silicon oxynitride (SiON), but are not limited thereto. However, the multi-buffer layer 141 and the active buffer layer 142 can be omitted depending on a structure or a characteristic of the display device 100.

[0092] In the meantime, the multi-buffer layer 141 and the active buffer layer 142 can be formed only above the plurality of first plate patterns 121 and the plurality of second plate patterns 123. The multi-buffer layer 141 and the active buffer layer 142 can overlap the area in which the first plate patterns 121 and the second plate patterns 123 are disposed. The multi-buffer layer 141 and the active buffer layer 142 may not be formed in an area between the plurality of first plate patterns 121 and an area between the plurality of second plate patterns 123. The multi-buffer layer 141 and the active buffer layer 142 which are formed of an inorganic material can be easily cracked to be damaged during a process of stretching the display device 100. Therefore, the multi-buffer layer 141 and the active buffer layer 142 are patterned to have a shape of the plurality of first plate patterns 121 and the plurality of second plate patterns 123 to be formed only above the plurality of first plate patterns 121 and the plurality of second plate patterns 123. Accordingly, in the display device 100 according to the example embodiment of the present disclosure, the multi-buffer layer 141 and the active buffer layer 142 are formed only in an area overlapping the plurality of first plate patterns 121 and the plurality of second plate patterns 123 which are rigid patterns. Therefore, even though the display device 100 is bent or stretched to be deformed, the damage of the multi-buffer layer 141 and the active buffer layer 142 is suppressed so that the damages of various components of the display device 100 can also be suppressed.

[0093] A light shielding layer BSM is disposed between the multi-buffer layer 141 and the active buffer layer 142. The light shielding layer BSM blocks light which is incident onto the active layer ACT of a transistor to be described below, below the substrate. Light which is incident onto the active layer ACT of the driving transistor DT is blocked by

the light shielding layer BSM to minimize a leakage current. The light shielding layer BSM can be formed of a single layer or a multi-layer formed of any one of molybdenum (Mo), copper (Cu), titanium (Ti), aluminum (Al), chrome (Cr), gold (Au), nickel (Ni), and neodymium (Nd) or an alloy thereof, but is not limited thereto.

[0094] A driving transistor DT is disposed on the active buffer layer **142**. The driving transistor DT includes an active layer ACT, a gate electrode GE, a source electrode SE, and a drain electrode DE.

[0095] First, the active layer ACT is disposed on the active buffer layer **142**. The active layer ACT can be formed of a semiconductor material, such as an oxide semiconductor, amorphous silicon, or polysilicon, but is not limited thereto.

[0096] The gate insulating layer **143** is disposed on the active layer ACT. The gate insulating layer **143** is an insulating layer which insulates the active layer ACT from the gate electrode GE and can be configured by a single layer or a double layer of silicon oxide (SiOx) or silicon nitride (SiNx), but is not limited thereto.

[0097] The gate electrode GE is disposed on the gate insulating layer **143**. The gate electrode GE can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0098] The first interlayer insulating layer **144** is disposed on the gate electrode GE and the second interlayer insulating layer **145** is disposed on the first interlayer insulating layer **144**. The first interlayer insulating layer **144** and the second interlayer insulating layer **145** are insulating layers which protect components therebelow and can be configured by a single layer or a double layer of silicon oxide (SiOx) or silicon nitride (SiNx), but are not limited thereto.

[0099] The source electrode SE and the drain electrode DE are disposed on the second interlayer insulating layer **145**. The source electrode SE and the drain electrode DE can be electrically connected to the active layer ACT through a contact hole formed in the second interlayer insulating layer **145**, the first interlayer insulating layer **144**, and the gate insulating layer **143**. The source electrode SE and the drain electrode DE can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), chrome (Cr), or an alloy thereof, but are not limited thereto.

[0100] Next, a first conductive layer CL**1** is disposed between the active buffer layer **142** and the gate insulating layer **143**. The first conductive layers CL**1** can configure at least a part of the plurality of wiring lines which supplies various signals to the sub pixel SPX or a configuration of the pixel circuit. For example, the first conductive layer CL**1** can be any one of various wiring lines, such as a scan line, a data line, a reference line, an initialization line, a high potential power line, and a low potential power line or can be a configuration included in a transistor or a capacitor. The first conductive layer CL**1** can be formed of the same material as the active layer ACT.

[0101] A second conductive layers CL**2** is disposed between the gate insulating layer **143** and the first interlayer insulating layer **144**. The second conductive layer CL**2** is an electrode which applies a voltage to the light shielding layer BSM. For example, the light shielding layer BSM is electrically connected to another configuration disposed on the first plate pattern **121** through a second conductive layer CL**2** to be applied with a voltage. The light shielding layer BSM which is applied with a voltage by means of the second conductive layer CL**2** does not operate as a floating gate and can minimize a fluctuation of a threshold voltage of the driving transistor DT which is generated by the floated light shielding layer BSM. The second conductive layer CL**2** can be formed of the same conductive material as the gate electrode GE and can be configured by a single layer or a multi-layered structure of copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0102] The power line PL is disposed between the first interlayer insulating layer **144** and the second interlayer insulating layer **145**. The power line PL is a wiring line which transmits a power voltage to the light emitting diode LED. The power line PL can be any one of a high potential power line or a low potential power line. The power line PL can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0103] A plurality of third conductive layers CL**3** is disposed between the first interlayer insulating layer **144** and the second interlayer insulating layer **145**. The plurality of third conductive layers CL**3** can configure at least a part of the plurality of wiring lines which supplies various signals to the sub pixel SP or a configuration of the pixel circuit. For example, one third conductive layer CL**3**, among the plurality of third conductive layers CL**3**, can overlap the gate electrode GE of the driving transistor DT to form a capacitor. As another example, the other third conductive layer CL**3**, among the plurality of third conductive layers CL**3** can serve as a plurality of wiring lines which transmits a signal to the sub pixel SP. The plurality of third conductive layers CL**3** can be formed of the same material on the same layer as the power line PL. The plurality of third conductive layers CL**3** can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0104] A plurality of fourth conductive layers CL**4** is disposed between the second interlayer insulating layer **145** and the third interlayer insulating layer **146**. The plurality of fourth conductive layers CL**4** can configure at least a part of the plurality of wiring lines which supplies various signals to the sub pixel SP or a configuration of the pixel circuit. The plurality of fourth conductive layers CL**4** connects wiring lines disposed on different layers and can serve as a part of the wiring line. For example, some of the plurality of fourth conductive layers CL**4** can electrically connect the second conductive layer CL**2** and a sixth conductive layer CL**6** and the others of the plurality of fourth conductive layers CL**4** can be electrically connected to the third conductive layer CL**3**. The plurality of fourth conductive layers CL**4** can be formed on the same layer with the same material as the source electrode SE and the drain electrode DE of the driving transistor DT. For example, the plurality of fourth conductive layers CL**4** can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel

(Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0105] The third interlayer insulating layer **146** is disposed on the plurality of fourth conductive layers CL**4**. The third interlayer insulating layer **146** is an insulating layer which protects components below the third interlayer insulating layer **146** and can be configured by a single layer or a double layer of silicon oxide (SiOx) or silicon nitride (SiNx), but is not limited thereto.

[0106] A plurality of fifth conductive layers CL**5** is disposed on the third interlayer insulating layer **146**. The plurality of fifth conductive layers CL**5** can configure at least a part of the plurality of wiring lines which supplies various signals to the sub pixel SP or a configuration of the pixel circuit. The plurality of fifth conductive layers CL**5** connects wiring lines disposed on different layers and can serve as a part of the wiring line. For example, a part of the plurality of fifth conductive layers CL**5** can electrically connect the first conductive layer CL**1** and the sixth conductive layer CL**6**. Further, the other fifth conductive layers CL**5**, among the plurality of fifth conductive layers CL**5** can electrically connect the power line PL and the first connection electrode CE**1**. The plurality of fifth conductive layers CL**5** can be configured by a single layer or a multi-layered structure of a conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0107] The passivation layer **147** is disposed on the plurality of fifth conductive layers CL**5**. The passivation layer **147** is an insulating layer which protects components below the passivation layer **147** and can be configured by a single layer or a double layer of silicon oxide (SiOx) or silicon nitride (SiNx), but is not limited thereto.

[0108] A first planarization layer **148** is disposed on the passivation layer **147**. The first planarization layer **148** can planarize an upper portion of the first plate pattern **121** on which a plurality of conductive layers, a driving transistor DT, and a plurality of wiring lines are disposed. The first planarization layer **148** can be configured by a single layer or a plurality of layers and can be formed of an organic material. For example, the first planarization layer **148** can be configured by a single layer or a double layer, and for example, can be formed of photoresist or an acrylic-based organic material, but is not limited thereto.

[0109] Referring to FIGS. **3** to **5**, the first connection electrode CE**1** is disposed on the first planarization layer **148** in each of the plurality of sub pixels SP. The first connection electrode CE**1** is an electrode which electrically connects the light emitting element LED and the power line PL. The first connection electrode CE**1** can be electrically connected to the power line PL through the fifth conductive layer CL**5**. Further, the electrode of the light emitting diode LED can be electrically connected to the first connection electrode CE**1**. The first connection electrode CE**1** can be configured by a single layer or a multi-layered structure of an opaque conductive material, such as copper (Cu), aluminum (Al), molybdenum (Mo), nickel (Ni), titanium (Ti), gold (Au), chrome (Cr), or an alloy thereof, but is not limited thereto.

[0110] In the first sub pixel SP**1**, the first light emitting diode **150** is disposed on the first connection electrode CE**1**. The first light emitting diode **150** is an element which emits light by a current and can be a light emitting diode (LED) or a micro LED, but is not limited thereto. At this time, the first light emitting diode **150** disposed in the first sub pixel SP**1** which is a red sub pixel SP can be a blue light emitting diode or a green light emitting diode. Further, a red light conversion layer CCL is further disposed in the first sub pixel SP**1** to convert light emitted from the first light emitting diode into red light to emit the converted red light.

[0111] The first light emitting diode **150** includes a first n-type semiconductor layer **151**, a first emission layer **152**, a first p-type semiconductor layer **153**, a first n-type electrode **154**, a first p-type electrode **155**, and a first encapsulation film **156**. The first light emitting diode **150** can be a vertical type light emitting diode LED in which the first n-type electrode **154** and the first p-type electrode **155** are disposed above and below the first emission layer **152**.

[0112] First, the first n-type semiconductor layer **151** is disposed on the first connection electrode CE**1** and the first p-type semiconductor layer **153** is disposed on the first n-type semiconductor layer **151**. The first n-type semiconductor layer **151** and the first p-type semiconductor layer **153** can be semiconductor layers doped with n-type and p-type impurities. For example, the first n-type semiconductor layer **151** and the first p-type semiconductor layer **153** can be layers doped with n-type and p-type impurities into a material such as gallium nitride (GaN), indium aluminum phosphide (InAlP), or gallium arsenide (GaAs). The p-type impurity can be magnesium (Mg), zinc (Zn), beryllium (Be), and the like, and the n-type impurity can be silicon (Si), germanium (Ge), tin (Sn), and the like, but are not limited thereto.

[0113] The first emission layer **152** is disposed between the first n-type semiconductor layer **151** and the first p-type semiconductor layer **153**. The first emission layer **152** is supplied with holes and electrons from the first n-type semiconductor layer **151** and the first p-type semiconductor layer **153** to emit light. The first emission layer **152** can be formed with a single layer or a multi-quantum well (MQW) structure, and for example, can be formed of indium gallium nitride (InGaN) or gallium nitride (GaN), but is not limited thereto.

[0114] The first n-type electrode **154** is disposed between the first n-type semiconductor layer **151** and the first connection electrode CE**1**. The first n-type electrode **154** is an electrode which electrically connects the first light emitting diode **150** and the power line PL. The first n-type electrode **154** can be in contact with a bottom surface of the first n-type semiconductor layer **151**. The first n-type electrode **154** is in contact with the first connection electrode CE**1** to be electrically connected to the first connection electrode CE**1**. The first n-type electrode **154** can be electrically connected to the power line PL through the first connection electrode CE**1** and the fifth conductive layer CL**5**. The first n-type electrode **154** can be configured by a conductive material, for example, a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO) or an opaque conductive material, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu) or an alloy thereof, but is not limited thereto.

[0115] The first p-type electrode **155** is disposed on the first p-type semiconductor layer **153**. The first p-type electrodes **155** is an electrode for electrically connecting the first light emitting diode **150** and the driving transistor DT. The first p-type electrodes **155** can be electrically connected to the source electrode SE or the drain electrode DE of the driving transistor DT through the second connection electrode CE**2**. The first p-type electrode **155** can be configured

by a conductive material, and for example, an opaque conductive material, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu), or an alloy thereof, but is not limited thereto.

[0116] A first encapsulation film **156** which encloses the first n-type semiconductor layer **151**, the first emission layer **152**, the first p-type semiconductor layer **153**, the first n-type electrode **154**, and the first p-type electrode **155** is disposed. The first encapsulation film **156** is formed of an insulating material to protect the first n-type semiconductor layer **151**, the first emission layer **152**, and the first p-type semiconductor layer **153**. Further, at least a part of the first n-type electrode **154** and the first p-type electrode **155** is exposed from the first encapsulation film **156** to electrically connect the first connection electrode CE**1** and the second connection electrode CE**2** to the first n-type electrode **154** and the first p-type electrode **155**. The first encapsulation film **156** is formed of an insulating material, such as silicon nitride (SiNx) or silicon oxide (SiOx), but is not limited thereto.

[0117] A second planarization layer **149** is disposed on the first light emitting diodes **150** and the first planarization layer **148**. The second planarization layer **149** is disposed so as to enclose the first light emitting diode **150** to fix and protect the first light emitting diode **150**. The second planarization layer **149** can be configured by a single layer or a plurality of layers and can be formed of an organic material. For example, the second planarization layer **149** can be configured by a single layer or a double layer, and for example, can be formed of photoresist or an acrylic-based organic material, but is not limited thereto.

[0118] The second connection electrode CE**2** is disposed on the second planarization layer **149** in the first sub pixel SP**1**. The second connection electrodes CE**2** is an electrode for electrically connecting the plurality of light emitting diodes LED and the driving transistor DT. The second connection electrodes CE**2** can be electrically connected to any one of the source electrode SE or the drain electrode DE of the driving transistor DT, through a contact hole formed in the second planarization layer **149**, the first planarization layer **148**, the passivation layer **147**, and the third interlayer insulating layer **146**. Further, the second connection electrodes CE**2** can be electrically connected to the first p-type electrode **155** of the first light emitting diode **150** exposed from the second planarization layer **149**. The second connection electrode CE**2** can be formed of a conductive material, for example, a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO), but is not limited thereto.

[0119] A plurality of sixth conductive layers CL**6** is disposed on the second planarization layer **149**. The plurality of sixth conductive layers CL**6** can configure at least a part of the plurality of wiring lines which supplies various signals to the sub pixel SP or a configuration of the pixel circuit. For example, some of the plurality of sixth conductive layers CL**6** is electrically connected to the fifth conductive layer CL**5** and the other sixth conductive layer can be electrically connected to the fourth conductive layer CL**4**. The plurality of sixth conductive layers CL**6** is formed of a conductive material, for example, a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO), but is not limited thereto.

[0120] A first reflective layer RL**1** is disposed on a side portion of the first light emitting diode **150** in the first sub pixel SP**1**. The first light emitting diode **150** can be disposed in an area between the first reflective layer RL**1** and the light conversion layer CCL. A V-shaped first groove **149***a* is disposed in a position of the second planarization layer **145** adjacent to the first light emitting diode **150** and the first reflective layer RL**1** can be disposed on a surface in the V-shaped first groove **149***a*. The first reflective layer RL**1** is a reflective layer which reflects light emitted from the first light emitting diode **150** to the light conversion layer CCL. The first light emitting diode **150** has one side surface facing the light conversion layer CCL and an opposite surface of one side surface. The first reflective layer RL**1** can be disposed so as to be face the opposite surface of one side surface of the first light emitting diode **150**. One side surface of the first light emitting diode **150** can face the light conversion layer CCL and the opposite surface of one side surface of the first light emitting diode **150** can face the first reflective layer RL**1**. The first reflective layer RL**1** can be formed of a material having a high reflection efficiency, and for example, an opaque conductive material, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu), or an alloy thereof, but is not limited thereto.

[0121] At this time, the first groove **149***a* and the first reflective layer RL**1** can be disposed to be spaced apart from the first light emitting diode **150**. If the first groove **149***a* is disposed so as to overlap the first light emitting diode **150** to expose the first light emitting diode **150** in the first groove **149***a* and cover the entire side surface of the first light emitting diode **150** by the first reflective layer RL**1**, the short defect that allows the first reflective layer RL**1** to electrically connect the first n-type electrode **154** and the first p-type electrode **155** can be caused. Therefore, the first groove **149***a* and the first reflective layer RL**1** can be disposed to be separated from the first light emitting diode **150**.

[0122] In the meantime, even though in the drawing, it is illustrated that a planar shape of the first reflective layer RL**1** has a straight line shape, the planar shape of the first reflective layer RL**1** is not limited thereto. For example, the planar shape of the first reflective layer RL**1** can enclose at least a part of remaining side surfaces of the first light emitting diodes **150**, excluding one side surface of the first light emitting diodes **150** facing the light conversion layer CCL.

[0123] As the first p-type electrode **155** is formed of an opaque conductive material, most of light emitted from the first light emitting diode **150** can be emitted to the lateral direction of the first light emitting diode **150**, rather than the upward direction. At this time, the first reflective layer RL**1** disposed on a side portion of the first light emitting diode **150** reflects light which travels to be far from the light conversion layer CCL, among light emitted from the first light emitting diode **150**, to the light conversion layer CCL again to improve the light conversion efficiency of the light conversion layer CCL.

[0124] Further, the first connection electrode CE**1** is formed of an opaque conductive material to improve the light conversion efficiency of the light conversion layer CCL. For example, the first connection electrode CE**1** formed of the opaque conductive material can reflect light which is directed to the lower portion of the first light emitting diode **150**, among light emitted from the first light emitting diode **150**. Further, the light reflected from the first connection electrode CE**1** can be reflected to the light conversion layer CCL by the first p-type electrode **155** and the first reflective layer RL**1**.

[0125] At this time, the second connection electrode CE**2** can be disposed on the first reflective layer RL**1**. At least a part of the second connection electrode CE**2** can be disposed in the first groove **149***a* of the second planarization layer **149** in which the first reflective layer RL**1** is located. Specifically, after forming the second planarization layer **149** which covers the first light emitting diode **150** and forming the first groove **149***a* in the second planarization layer **149**, the first reflective layer RL**1** can be formed in the first groove **149***a*. Next, the second connection electrode CE**2** can be formed on the second planarization layer **149** and the first reflective layer RL**1**. Accordingly, the process is performed in the order of the first reflective layer RL**1** and the second connection electrode CE**2** so that the first reflective layer RL**1** and the second connection electrode CE**2** can be in contact with each other in the first groove **149***a*.

[0126] In the meantime, a part of the second planarization layer **149** is disposed between the first reflective layer RL**1** and the first light emitting diode **150** so that the first reflective layer RL**1** can be disposed to be spaced apart from the first light emitting diode **150** and the first connection electrode CE**1**. Therefore, a short defect which is caused when the first reflective layer RL**1** which is in contact with the second connection electrode CE**2** is connected to the first connection electrode CE**1** or the first n-type electrode **154** can be suppressed.

[0127] A second groove **149***b* is formed in the second planarization layer **149** and the light conversion layer CCL is disposed in the second groove **149***b*. Referring to FIGS. **2** and **3**, the second groove **149***b* of the second planarization layer **149** can be disposed on a side portion of the first light emitting diode **150** in the first sub pixel SP**1**. The second groove **149***b* can extend to be long toward one direction. The second groove **149***b* and the first groove **149***a* can be disposed on one straight line and the first light emitting diode **150** can be disposed between the second groove **149***b* and the first groove **149***a*. The first light emitting diode **150** and the first reflective layer RL**1** can be disposed along a length direction of the light conversion layer CCL.

[0128] The light conversion layer CCL disposed in the second groove **149***b* can convert light emitted from the first light emitting diode **150** into red light. The light conversion layer CCL can include a color conversion material, such as a quantum dot, a nano fluorescent material or an organic fluorescent material. The color conversion material included in the light conversion layer CCL absorbs light emitted from the first light emitting diode **150** to emit light having a different wavelength. Light which is incident from the first light emitting diode **150** and the first reflective layer RL**1** onto the light conversion layer CCL is converted into red light by the light conversion layer CCL to be emitted to the outside of the display device **100**.

[0129] A second reflective layer RL**2** is disposed between the second groove **149***b* and the light conversion layer CCL. The second reflective layer RL**2** can reflect red light which is converted by the light conversion layer CCL to the upper portion of the light conversion layer CCL. The second reflective layer RL**2** can be disposed on an inner surface, other than an inner surface of the second groove **149***b* which faces to the first light emitting diode **150**, among a plurality of inner surfaces of the second groove **149***b*. For example, the second reflective layer RL**2** can be disposed on three inner surfaces, other than one inner surface which is opposite to the first light emitting diode **150**, among four inner surfaces of the second groove **149***b* and a bottom surface of the second groove **149***b*. Therefore, light from the first light emitting diode **150** can travel to the light conversion layer CCL through one surface of the second groove **149***b* in which the second reflective layer RL**2** is not disposed. For example, the second reflective layer RL**2** can be formed of an opaque conductive material having a high reflection efficiency, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu), or an alloy thereof, but is not limited thereto.

[0130] Next, referring to FIGS. **2**, **4**, and **5**, a plurality of connection lines **130** is disposed on the plurality of line patterns. The plurality of connection lines **130** refers to wiring lines which electrically connect the pads on the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. The plurality of connection lines **130** is disposed on the plurality of first line patterns **122** and the plurality of second line patterns **124**. The plurality of connection lines **130** can extend onto the plurality of first plate patterns **121** to be electrically connected to the plurality of pads on the plurality of first plate patterns **121**. The plurality of first line patterns **122** is not disposed in an area where the plurality of connection lines **130** is not disposed, among areas between the plurality of first plate patterns **121**. Further, the plurality of connection lines **130** is disposed on the plurality of second line patterns **124** to be electrically connected to a pad on the plurality of second plate patterns **123** and a pad on the plurality of first plate patterns **121**.

[0131] The plurality of connection lines **130** includes a first connection line **131** and a second connection line **132**. The first connection line **131** and the second connection line **132** are disposed between the plurality of first plate patterns **121**, between the plurality of second plate patterns **123**, and between the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. Specifically, the first connection line **131** refers to a wiring line extending in the first direction D**1** between the plurality of first plate patterns **121**, between the plurality of second plate patterns **123**, and between the plurality of first plate patterns **121** and the plurality of second plate patterns **123**, among the connection lines **130**. The second connection line **132** refers to a wiring line extending in the second direction D**2** between the plurality of first plate patterns **121**, between the plurality of second plate patterns **123**, and between the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. Here, the first direction D**1** and the second direction D**2** can also be referred to as a row direction and a column direction, respectively.

[0132] The plurality of connection lines **130** can be formed of a conductive material. For example, the plurality of connection lines **130** can be formed of a metal material such as copper (Cu), aluminum (Al), titanium (Ti), and molybdenum or a stacked structure of metal materials such as copper/molybdenum-titanium (Cu/Moti) or titanium/aluminum/titanium (Ti/Al/Ti), but is not limited thereto.

[0133] In the case of a general display device, various wiring lines such as a plurality of scan lines and a plurality of data lines extend between the plurality of sub pixels with a straight line shape and the plurality of sub pixels is connected to one signal line. Therefore, in the general display device, various wiring lines, such as a scan line, a data line, a high potential voltage line, and a reference voltage line, extend from one side to the other side of the display device without being disconnected on the substrate.

[0134] In contrast, in the display device **100** according to the example embodiment of the present disclosure, various wiring lines, such as a scan line, a data line, a high potential voltage line, a reference voltage line, and an initialization voltage line having a straight line shape which are considered to be used for the general display device, are disposed only on the plurality of first plate patterns **121** and the plurality of second plate patterns **123**. For example, in the display device **100** according to the example embodiment of the present disclosure, a straight line-shaped wiring line is disposed only on the plurality of first plate patterns **121** and the plurality of second plate patterns **123**.

[0135] In the display device **100** according to the example embodiment of the present disclosure, the pads on two adjacent first plate patterns **121** can be connected by the connection lines **130**. Accordingly, the connection line **130** electrically connects the pads on two adjacent first plate patterns **121**. Accordingly, the display device **100** according to the example embodiment of the present disclosure can include a plurality of connection lines **130** so as to electrically connect various wiring lines, such as a scan line, a data line, a high potential voltage line, and a reference voltage line, between the plurality of first plate patterns **121**. For example, the scan line can be disposed on the plurality of first plate patterns **121** disposed to be adjacent to each other in the first direction D**1** and the pads can be disposed on both ends of the scan line. At this time, the plurality of pads on the plurality of first plate patterns **121** adjacent to each other in the first direction D**1** can be connected to each other by the first connection line **131** which serves as a scan line. Therefore, the scan line disposed on the plurality of first plate patterns **121** and the first connection line **131** disposed on the first line pattern **122** can serve as one scan line. Further, wiring lines which extend in the first direction D**1**, among all various wiring lines which can be included in the display device **100**, such as an emission signal line, a low potential voltage line, and a high potential voltage line, can also be electrically connected by the first connection line **131**, as described above.

[0136] A plurality of first connection lines **131** of the active area AA can connect the pads on two first plate patterns **121** which are disposed side by side, among the pads on the plurality of first plate patterns **121** disposed to be adjacent in the first direction D**1**. For example, the pads on the plurality of first plate patterns **121** disposed in the first direction D**1** can be connected by the first connection line **131** serving as a scan line and transmit a scan signal to each of the plurality of sub pixels SP. However, the plurality of first connection lines **131** can connect an emission signal line, a high potential voltage line, or a low potential voltage line, in addition to the scan line, but is not limited thereto.

[0137] A plurality of second connection lines **132** can connect the pads on two first plate patterns **121** which are disposed side by side, among the plurality of first plate patterns **121** disposed to be adjacent in the second direction D**2**. An internal line on the plurality of first plate patterns **121** disposed in the second direction D**2** can be connected by the plurality of second connection lines **132** serving as a data line and transmit a data voltage to each of the plurality of sub pixels SP. However, the plurality of second connection lines **132** can connect data lines, high potential voltage lines, low potential voltage lines, or reference lines, but is not limited thereto.

[0138] Further, referring to FIGS. **4** and **5**, end portions of the plurality of connection lines **130** can be connected to the pads on the first plate patterns **121**. For example, the fifth conductive layer CL**5** which serves as a pad is disposed on the third interlayer insulating layer **146** of the first plate pattern **121**. Any one of the plurality of connection lines **130** extends from the first line pattern **122** to side surfaces and a top surface of the first planarization layer **148** and can be electrically connected to the fifth conductive layer CL**5** through a contact hole. Further, another one of the plurality of connection lines **130** extends to a side surface and a top surface of the second planarization layer **149** to be electrically connected to a pad on the first plate pattern **121**.

[0139] Next, referring to FIGS. **2** and **4**, in the second sub pixel SP**2**, the second light emitting diode **160** is disposed on the first planarization layer **148**. A second light emitting diode **160** which is a green light emitting diode is disposed in the second sub pixel SP**2** which is a green sub pixel SP. The second light emitting diode **160** can be a flip-chip type light emitting diode LED in which a second n-type electrode **164** and a second p-type electrode **165** are disposed in a horizontal direction below a second emission layer **162**. Therefore, as compared with the first sub pixel SP**1**, a placement structure of the second connection electrode CE**2** for connecting the second light emitting diode **160** and the driving transistor DT can be different in the second sub pixel SP**2**.

[0140] First, the first connection electrode CE**1** and the second connection electrode CE**2** can be disposed on the first planarization layer **148**. The first connection electrode CE**1** can be connected to the fifth conductive layer CL**5** through a contact hole formed in the first planarization layer **148** and the passivation layer **147**. Therefore, the first connection electrode CE**1** can be electrically connected to the power line PL through the fifth conductive layer CL**5**. Further, the second connection electrodes CE**2** can be electrically connected to any one of the source electrode SE or the drain electrode DE of the driving transistor DT, through a contact hole formed in the first planarization layer **148**, the passivation layer **147**, and the third interlayer insulating layer **146**.

[0141] Further, the second light emitting diode **160** is disposed on the first connection electrode CE**1** and the second connection electrode CE**2**. The second light emitting diode **160** includes a second n-type semiconductor layer **161**, a second emission layer **162**, a second p-type semiconductor layer **163**, a second n-type electrode **164**, a second p-type electrode **165**, and a second encapsulation film **166**.

[0142] Specifically, the second p-type semiconductor layer **163** is disposed on the first connection electrode CE**1** and the second connection electrode CE**2** and the second n-type semiconductor layer **161** is disposed on the second p-type semiconductor layer **163**. The second n-type semiconductor layer **161** and the second p-type semiconductor layer **163** can be semiconductor layers doped with n-type and p-type impurities. For example, the second n-type semiconductor layer **161** and the second p-type semiconductor layer **163** can be layers doped with n-type and p-type impurities into a material such as gallium nitride (GaN), indium aluminum phosphide (InAlP), or gallium arsenide (GaAs). The p-type impurity can be magnesium (Mg), zinc (Zn), and beryllium (Be), and the n-type impurity can be silicon (Si), germanium (Ge), and tin (Sn), but are not limited thereto.

[0143] The second emission layer **162** is disposed between the second n-type semiconductor layer **161** and the second p-type semiconductor layer **163**. The second emission layer **162** is supplied with holes and electrons from the second n-type semiconductor layer **161** and the second p-type semiconductor layer **163** to emit light. The second emission layer **162** can be formed by a single layer or a multi-quantum well (MQW) structure, and for example, can be formed of indium gallium nitride (InGaN) or gallium nitride (GaN), but is not limited thereto.

[0144] The second n-type electrode **164** is disposed between the second n-type semiconductor layer **161** and the first connection electrode CE**1**. The second n-type electrode **164** is an electrode which electrically connects the second light emitting diode **160** and the power line PL. The second n-type electrode **164** can be in contact with a bottom surface of the second n-type semiconductor layer **162** which protrudes from the second emission layer **162** and the second p-type semiconductor layer **163**. Further, the second n-type electrode **164** is in contact with the first connection electrode CE**1** to be electrically connected to the first connection electrode CE**1**. Therefore, the second n-type electrode **164** can be electrically connected to the power line PL through the first connection electrode CE**1** and the fifth conductive layer CL**5**. The second n-type electrode **164** can be configured by a conductive material, for example, a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO) or an opaque conductive material, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu) or an alloy thereof, but is not limited thereto.

[0145] The second p-type electrode **165** is disposed between the second p-type semiconductor layer **163** and the second connection electrode CE**2**. The second p-type electrodes **165** is an electrode for electrically connecting the second light emitting diode **160** and the driving transistor DT. The second p-type electrode **165** can be electrically connected to any one of the source electrode SE or the drain electrode DE of the driving transistor DT through the second connection electrode CE**2**. The second p-type electrode **165** can be configured by a conductive material, for example, a transparent conductive material, such as indium tin oxide (ITO) or indium zinc oxide (IZO) or an opaque conductive material, such as titanium (Ti), gold (Au), silver (Ag), copper (Cu) or an alloy thereof, but is not limited thereto.

[0146] A second encapsulation film **166** which encloses the second n-type semiconductor layer **161**, the second emission layer **162**, the second p-type semiconductor layer **163**, the second n-type electrode **164**, and the second p-type electrode **165** is disposed. The second encapsulation film **166** is formed of an insulating material to protect the second n-type semiconductor layer **161**, the second light emitting layer **162**, and the second p-type semiconductor layer **163**. Further, at least a part of the second n-type electrode **164** and the second p-type electrode **165** is exposed from the second encapsulation film **166** to electrically connect the first connection electrode CE**1** and the second connection electrode CE**2** to the second n-type electrode **164** and the second p-type electrode **165**. The second encapsulation film **166** can be formed of an insulating material, such as silicon nitride (SiNx) or silicon oxide (SiOx), but is not limited thereto.

[0147] In the meantime, the second light emitting diode **160** disposed in the second sub pixel SP**2** which is a green sub pixel SP is a green light emitting diode so that a separate light conversion layer CCL for converting green light from the second light emitting diode **160** is not disposed in the second sub pixel SP**2**. For example, in the second sub pixel SP**2**, green light from the second light emitting diode **160** can emit to the outside of the display device **100** as it is.

[0148] A conductive adhesive layer AD is disposed between the second light emitting diode **160** and the first connection electrode CE**1** and between the second light emitting diode **160** and the second connection electrode CE**2**. The conductive adhesive layer AD can be disposed between the second n-type electrode **164** and the second p-type electrode **165** of the second light emitting diode **160** and the first connection electrode CE**1** and the second connection electrode CE**2**. The conductive adhesive layer AD can be an adhesive layer in which conductive balls are dispersed in an insulating base member. When heat or pressure is applied to the conductive adhesive layer AD, the conductive balls are electrically connected in a portion applied with heat or pressure to have a conductive property and an area which is not pressurized can have an insulating property. Accordingly, the second light emitting diode **160** is disposed on the conductive adhesive layer AD and heat or pressure is applied thereto to electrically connect the second n-type electrode **164** and the second p-type electrode **165** of the second light emitting diode **160** and the first connection electrode CE**1** and the second connection electrode CE**2**. At this time, it is illustrated that the conductive adhesive layers AD which cover the first connection electrode CE**1** and the second connection electrode CE**2** are connected. However, the conductive adhesive layers AD can be separated to be disposed above the first connection electrode CE**1** and the second connection electrode CE**2**, respectively.

[0149] Next, referring to FIG. **5**, the third sub pixel SP**3** can be a blue sub pixel SP which emits blue light. Further, a structure of the third sub pixel SP**3** can be substantially the same as the structure of the second sub pixel SP**2**. Specifically, the first connection electrode CE**1** and the second connection electrode CE**2** can be disposed on the first planarization layer **148** also in the third sub pixel SP**3**.

[0150] Further, in the third sub pixel SP**3**, the third light emitting diode **170** which emits blue light can be disposed. The third light emitting diode **170** can be substantially the same as the second light emitting diode **160**, except that blue light is emitted. Therefore, a separate light conversion layer CCL may not be disposed in the third sub pixel SP**3**.

[0151] Specifically, the third light emitting diode **170** includes a third n-type semiconductor layer **171**, a third emission layer **172**, a third p-type semiconductor layer **173**, a third n-type electrode **174**, a third p-type electrode **175**, and a third encapsulation film **176**. The third light emitting diode **170** can be a flip-chip type light emitting diode LED in which a third n-type electrode **174** and a third p-type electrode **175** are disposed in a horizontal direction below a third emission layer **172**.

[0152] The third n-type semiconductor layer **171**, the third p-type semiconductor layer **173**, the third n-type electrode **174**, the third p-type electrode **175**, and the third encapsulation film **176** of the third light emitting diode **170** can be substantially the same as the second n-type semiconductor layer **161**, the second p-type semiconductor layer **163**, the second n-type electrode **164**, the second p-type electrode **165**, and the second encapsulation film **166**. Further, the third emission layer **172** of the third light emitting diode **170** emits blue light and the second emission layer **162** of the second light emitting diode **160** can emit green light.

[0153] In the meantime, in the present disclosure, it is described that the second light emitting diode **160** of the second sub pixel SP**2** and the third light emitting diode **170** of the third sub pixel SP**3** are flip-chip types. However, the second light emitting diode **160** and the third light emitting diode **170** can have the vertical structure which is the same as the first light emitting diode **150** or can have a lateral structure, but are not limited thereto.

[0154] Further, in the present disclosure, it is described that the second light emitting diode **160** and the third light emitting diode **170** which emit green light and blue light are disposed in the second sub pixel SP**2** and the third sub pixel SP**3**, respectively so that a green light conversion layer and a blue light conversion layer are not disposed in the second sub pixel SP**2** and the third sub pixel SP**3**. However, a green light conversion layer and a blue light conversion layer can be further disposed in the second sub pixel SP**2** and the third sub pixel SP**3**, respectively, but are not limited thereto.

[0155] In the third sub pixel SP**3** which is a blue sub pixel SP, a third light emitting diode **170** which emits blue light is disposed so that there is no need to dispose a separate light conversion layer CCL. Further, in the second sub pixel SP**2** which is a green sub pixel SP, a second light emitting diode **160** which emits green light is disposed so that there is no need to dispose a separate light conversion layer CCL. Therefore, the second light emitting diode **160** and the third light emitting diode **170** which emit green light and blue light are disposed in the second sub pixel SP**2** and the third sub pixel SP**3** so that green and blue images can be displayed.

[0156] In the meantime, the first light emitting diode **150** disposed in the first sub pixel SP**1** which is a red sub pixel SP emits green light or blue light so that a light conversion layer CCL for converting green light or blue light from the first light emitting diode **150** can be further disposed in the first sub pixel SP**1**. Specifically, the red light emitting diode which emits red light can have an efficiency inferior to the green light emitting diode and the blue light emitting diode. Therefore, in the first sub pixel SP**1**, the light conversion layer CCL is further formed in the green light emitting diode or the blue light emitting diode which has a better efficiency, instead of the red light emitting diode, to implement red light.

[0157] Further, in the related art, a light conversion efficiency of the light conversion layer is increased by disposing the light conversion layer above the light emitting diode and forming the light conversion layer to have a larger thickness. However, there are problem in that a process time or a manufacturing cost required to form the light conversion layer to have a large thickness is limited and it is difficult to increase the light conversion efficiency to a predetermined level or higher.

[0158] Accordingly, in the display device **100** according to the example embodiment of the present disclosure, a light conversion layer CCL having a length which is long in a horizontal direction is formed on a side portion of the first light emitting diode **150** to increase a light conversion efficiency of the light conversion layer CCL. The light conversion layer CCL has a length long in the horizontal direction so that a probability of absorbing and converting light which moves toward the light conversion layer CCL in the horizontal direction in a light conversion material. Finally, a light conversion efficiency is improved. Further, the first p-type electrode **155** of the first light emitting diode **150** is formed of an opaque conductive material. The first reflective layer RL**1** which reflects light from the first light emitting diode **150** to the light conversion layer CCL is formed on a side portion of the first light emitting diode **150** to transmit more light to the light conversion layer CCL. Accordingly, the light conversion layer CCL which has a length long in the horizontal direction is formed on a side portion of the first light emitting diode **150**. The light from the first light emitting diode **150** is reflected to the light conversion layer CCL to improve the light conversion efficiency of the light conversion layer CCL.

[0159] FIG. **6** is an enlarged plan view of an active area of a display device according to another example embodiment of the present disclosure. FIG. **7** is a cross-sectional view of a first sub pixel of a display device according to another example embodiment of the present disclosure. The only difference between a display device **600** of FIGS. **6** and **7** and the display device **100** of FIGS. **1** to **5** is a first plate pattern **121** and a first sub pixel SP**1**, but other configurations are the same or substantially the same, so that a redundant description will be omitted or may be briefly provided.

[0160] Referring to FIGS. **6** and **7**, each of a plurality of first plate patterns **121** of a display device **600** according to another example embodiment of the present disclosure has a protrusion **121***a* which extends in an inclined direction from the first plate pattern **121**. For example, a planar shape of the first plate pattern **121** can be a rectangular shape and the protrusion **121***a* can be a part which protrudes from any one of four corners of the first plate pattern **121** toward a malleable area SA.

[0161] The plurality of first plate patterns **121** is disposed to form a plurality of rows and a plurality of columns along the first direction D**1** and the second direction D**2**. A plurality of connection lines **130** extending in the first direction D**1** and the second direction D**2** can be disposed between the plurality of first plate patterns **121**. At this time, a malleable area SA in a diagonal direction of the plurality of first plate patterns **121**, for example, a malleable area SA in an inclined direction to the first direction D**1** and the second direction D**2** can be an empty space in which the connection line **130** or the first plate pattern **121** is not disposed. Further, in the empty space in which the first plate pattern **121** and the connection line **130** are not disposed, the protrusion **121***a* of the first plate pattern **121** can be disposed.

[0162] The protrusion **121***a* can be an area in which the light conversion layer CCL is disposed. The protrusion **121***a* in which the light conversion layer CCL is disposed can be an area included in the first sub pixel SP**1**. The first sub pixel SP**1** can include an area on the first plate pattern **121** and an area on the protrusion **121***a*. The first sub pixel SP**1** can be disposed in both a rigid area RA corresponding to the first plate pattern **121** and a malleable area SA corresponding to the protrusion **121***a*. In contrast, the second sub pixel SP**2** and the third sub pixel SP**3** can be disposed in the rigid area RA corresponding to the first plate pattern **121**.

[0163] A multi-buffer layer **141**, an active buffer layer **142**, a gate insulating layer **143**, a first interlayer insulating layer **144**, a second interlayer insulating layer **145**, a third interlayer insulating layer **146**, a passivation layer **147**, a first planarization layer **148**, and a second planarization layer **149** can be disposed on the protrusion **121***a* of the first plate pattern **121**. A plurality of insulating layers disposed on the

first plate pattern **121** can be disposed to extend to the protrusion **121***a*. Accordingly, the plurality of insulating layers which is the same as those disposed on the first plate pattern **121** is disposed on the protrusion **121***a* to minimize a step of the first light emitting diode **150** disposed on the first plate pattern **121** and the light conversion layer CCL disposed on the protrusion **121***a*.

[0164] A second groove **149***b* can be disposed in the second planarization layer **149** on the protrusion **121***a*. The second groove **149***b* of the second planarization layer **149** can be disposed so as to correspond to the protrusion **121***a*. Further, the light conversion layer CCL is disposed in the second groove **149***b* of the second planarization layer **149**. The light conversion layer CCL is disposed on the protrusion **121***a* to convert light from the first light emitting diode **150** into red light.

[0165] At this time, the light conversion layer CCL can extend in an inclined direction to the first direction D**1** and the second direction D**2**, like the protrusion **121***a*. The first light emitting diode **150** is aligned to face the light conversion layer CCL. The first reflective layer RL**1** can be also disposed to be aligned to be inclined toward the light conversion layer CCL. The first reflective layer RL**1**, the first light emitting diode **150**, and the light conversion layer CCL can be disposed along an inclined direction in one line.

[0166] Accordingly, in the display device **600** according to another example embodiment of the present disclosure, the light conversion layer CCL can be disposed in the malleable area SA in which the plurality of first plate patterns **121** and the plurality of connection lines **130** are not disposed. The plurality of first plate patterns **121** is disposed to form the plurality of rows and the plurality of columns. The plurality of connection lines **130** disposed along the first direction D**1** and the second direction D**2** can be disposed between the plurality of first plate patterns **121**. Therefore, a diagonal area of the plurality of first plate patterns **121** is an empty area in which the first plate pattern **121** or the connection line **130** is not disposed and can be a malleable area SA. The protrusion **121***a* extending from the first plate pattern **121** is disposed in the malleable area SA and the plurality of insulating layers and the light conversion layer CCL are disposed on the protrusion **121***a* to convert light from the first light emitting diode **150** into red light. The empty space is utilized as an area in which the protrusion **121***a* and the light conversion layer CCL are disposed to easily form the light conversion layer CCL in the display device **600** without being limited to a size on the first plate pattern **121**. Accordingly, in the display device **600** according to another example embodiment of the present disclosure, the light conversion layer CCL is formed in the malleable area SA in the diagonal direction of the plurality of first plate patterns **121** to easily convert light from the first light emitting diode **150**.

[0167] FIG. **8** is an enlarged plan view of an active area of a display device according to still another example embodiment of the present disclosure. FIG. **9** is a cross-sectional view of a first sub pixel of a display device according to still another example embodiment of the present disclosure. The only difference between a display device **800** of FIGS. **8** and **9** and the display device **100** of FIGS. **1** to **5** is a first sub pixel SP**1**, but other configurations are the same or substantially the same, so that a redundant description will be omitted or may be briefly provided.

[0168] Referring to FIGS. **8** and **9**, the light conversion layer CCL is disposed on some first line pattern **122** among the plurality of first line patterns **122**. For example, the light conversion layer CCL of the first sub pixel SP**1** can be disposed in one of the plurality of first line patterns **122** extending in the first direction D**1**. The light conversion layer CCL can be disposed on a partial area of the first line pattern **122** adjacent to the first plate pattern **121**, among the first line patterns **122**. The light conversion layer CCL can be disposed on the malleable area SA corresponding to the first line pattern **122**. As the light conversion layer CCL is disposed on the first line pattern **122**, the first sub pixel SP**1** can include an area on the first plate pattern **121** and an area on the first line pattern **122**. The first sub pixel SP**1** can be disposed in both a rigid area RA corresponding to the first plate pattern **121** and a malleable area SA corresponding to the first line pattern **122**. Further, the first line pattern **122** in which the light conversion layer CCL is disposed can include a part in which the light conversion layer CCL is disposed and a part in which the connection line **130** is disposed.

[0169] Further, in order to minimize a step between the light conversion layer CCL disposed on the first line pattern **122** and the first light emitting diode **150** disposed on the first planarization layer **148** of the first plate pattern **121**, a plurality of insulating layers can also be disposed on the first line pattern **122**. For example, a multi-buffer layer **141**, an active buffer layer **142**, a gate insulating layer **143**, a first interlayer insulating layer **144**, a second interlayer insulating layer **145**, a third interlayer insulating layer **146**, a passivation layer **147**, a first planarization layer **148**, and a second planarization layer **149** can be disposed between the first line pattern **122** and the light conversion layer CCL. Accordingly, the light conversion layer CCL disposed on the first line pattern **122** and the first light emitting diode **150** disposed on the first plate pattern **121** are disposed at the substantially same height to face each other. The light from the first light emitting diode **150** can be easily transmitted to the light conversion layer CCL.

[0170] A second groove **149***b* is disposed in the second planarization layer **149** disposed on the first line pattern **122** and the light conversion layer CCL can be disposed in the second groove **149***b*. In the area which overlaps the first line pattern **122**, the second groove **149***b* is formed in the second planarization layer **149** to dispose the light conversion layer CCL in the area on the first line pattern **122**.

[0171] In the meantime, the plurality of lines on the first plate pattern **121** is electrically connected to the connection line **130** on the first line pattern **122** to be applied with a signal. In this case, an end portion of each of the plurality of connection lines **130** extends onto the first plate pattern **121** to be connected to a pad on the first plate pattern **121** or be directly connected to the plurality of lines on the first plate pattern **121**.

[0172] Therefore, as the light conversion layer CCL is disposed on a part of the first line pattern **122** adjacent to the first plate pattern **121**, the plurality of wiring lines on the first plate pattern **121** and the connection line **130** on the first line pattern **122** can be connected to each other through a separate contact hole CH. For example, referring to FIG. **8**, any one of the plurality of sixth conductive layers CL**6** disposed on the first plate pattern **121** can be electrically connected to the connection line **130** through a contact hole CH formed in a partial area of the first line pattern **122**

corresponding to the first sub pixel SP**1**. An end portion of the connection line **130** is disposed in a partial area of the first line pattern **122** corresponding to the first sub pixel SP**1**. The sixth conductive layer CL**6** can be electrically connected to an end portion of the connection line **130** through a contact hole CH formed in the second planarization layer **149**, the first planarization layer **148**, the passivation layer **147**, the third interlayer insulating layer **146**, the second interlayer insulating layer **145**, the first interlayer insulating layer **144**, the gate insulating layer **143**, the active buffer layer **142**, and the multi-buffer layer **141**. However, a connection structure of the connection line **130** is illustrative, but is not limited thereto.

[0173] Next, the first light emitting diode **150** can be disposed to be adjacent to the light conversion layer CCL. The first light emitting diode **150** can be disposed to be adjacent to the first line pattern **122**. The first light emitting diode **150** on the first plate pattern **121** and the light conversion layer CCL on the first line pattern **122** can be disposed to face each other.

[0174] Further, the first reflective layer RL**1** can be disposed to face an opposite surface of one side surface of the first light emitting diode **150** which faces the light conversion layer CCL. One side surface of the first light emitting diode **150** can face the light conversion layer CCL and the opposite surface of one side surface of the first light emitting diode **150** can face the first reflective layer RL**1**. The first reflective layer RL**1**, the first light emitting diode **150**, and the light conversion layer CCL can be disposed along a length direction of the light conversion layer CCL in one line. Accordingly, light which travels to be far from the light conversion layer CCL, among light from the first light emitting diode **150** can be reflected to the light conversion layer CCL, by the first reflective layer RL**1**. Further, light which upwardly travels, among light emitted from the first emission layer **152** of the first light emitting diode **150** can be reflected to the light conversion layer CCL by the first p-type electrode **155** and the first reflective layer RL**1**.

[0175] Accordingly, in the display device **800** according to still another example embodiment of the present disclosure, the light conversion layer CCL can be disposed on the first line pattern **122**. The light conversion layer CCL can be disposed on a partial area of the first line pattern **122** adjacent to the first plate pattern **121**. The light conversion layer CCL is disposed on a partial area on the first line pattern **122** without being limited to an area on the first plate pattern **121**. Further, a plurality of insulating layers is disposed on the first line pattern **122** to minimize the step of the light conversion layer CCL on the first line pattern **122** and the first light emitting diode **150** on the first plate pattern **121** to easily transmit light from the first light emitting diode **150** to the light conversion layer CCL. Accordingly, the light conversion layer CCL is formed by utilizing an area on the first line pattern **122** to easily convert light from the first light emitting diode **150** into red light.

[0176] FIG. **10** is an enlarged plan view of an active area of a display device according to still another example embodiment of the present disclosure. FIG. **11** is a cross-sectional view of a first sub pixel of a display device according to still another example embodiment of the present disclosure. The only difference between a display device **1000** of FIGS. **10** and **11** and the display device **100** of FIGS. **1** to **5** is a first sub pixel SP**1**, but other configurations are the same or substantially the same, so that a redundant description will be omitted or may be briefly provided.

[0177] Referring to FIGS. **10** and **11**, the first light emitting diode **150** of the first sub pixel SP**1** and the light conversion layer CCL are disposed on the first line pattern **122**. The first light emitting diode **150** of the first sub pixel SP**1** and the light conversion layer CCL are disposed in the malleable area SA corresponding to the first line pattern **122** and the pixel circuit of the first sub pixel SP**1** is disposed in the rigid area RA corresponding to the first plate pattern **121**.

[0178] First, the connection line **130** connected to the first connection electrode CE**1** can be disposed on the first line pattern **122**. The connection line **130** extends from the first line pattern **122** onto the first planarization layer **148** of the first plate pattern **121** to be electrically connected to the first connection electrode CE**1** on the first planarization layer **148**. The connection line **130** can be in contact with a top surface of the first line pattern **122**, a side surface of the first planarization layer **148**, and a top surface of the first planarization layer **148**. Further, the connection line **130** can be connected to the first connection electrode CE**1** disposed on the top surface of the first planarization layer **148**.

[0179] The first light emitting diode **150** is disposed on the first line pattern **122** and the connection line **130** in the malleable area SA. The first n-type electrode **154** is in contact with the top surface of the connection line **130** so that the first light emitting diode **150** can be electrically connected to the connection line **130** and the first connection electrode CE**1**.

[0180] Next, the second planarization layer **149** is disposed on the first planarization layer **148**, the first connection electrode CE**1**, the connection line **130**, and the first light emitting diode **150**. The second planarization layer **149** can be disposed in at least a part of a rigid area RA in which the first plate pattern **121** is disposed and a malleable area SA in which the first line pattern **122** is disposed. The second planarization layer **149** can cover an end portion of the connection line **130** disposed on the first planarization layer **148**. Further, the second planarization layer **149** can be disposed in a partial area on the first line pattern **122** in which the first light emitting diode **150** and the light conversion layer CCL are located. The second planarization layer **149** can be disposed so as to cover a part of the first light emitting diode **150** and the connection line **130** in the area on the first line pattern **122**.

[0181] The first reflective layer RL**1** is disposed in the first groove **149***a* of the second planarization layer **149**. The first groove **149***a* and the first reflective layer RL**1** can overlap a partial area of the first line pattern **122** adjacent to the first plate pattern **121** and the connection line **130**. At this time, the connection line **130** may not be exposed from the first groove **149***a* so as not to cause a short defect caused when the first reflective layer RL**1** is connected to both the first connection electrode CE**1** and the connection line **130** and the second connection electrode CE**2**. A depth of the first groove **149***a* is formed to be shallower than a thickness of the second planarization layer **149**. Therefore, the first groove **149***a* of the second planarization layer **149** is disposed so as to overlap the connection line **130**, but the first groove **149***a* is formed to be shallower than the thickness of the second planarization layer **149** so that the connection line **130** may not be exposed from the first groove **149***a*. Accordingly, in the first groove **149***a*, the first reflective layer RL**1** and the connection line **130** are separated so as

not to be connected and the defect that the first connection electrode CE**1** and the connection line **130** are connected to the second connection electrode CE**2** through the first reflective layer RL**1** can be suppressed.

[0182] The light conversion layer CCL is disposed in the second groove **149***b* of the second planarization layer **149**. The second groove **149***b* and the light conversion layer CCL can be disposed on the first line pattern **122** and the connection line **130**. The light conversion layer CCL is disposed in an area of the first light emitting diode **150** in a lateral direction on the first line pattern **122** to convert light from the first light emitting diode **150** into red light.

[0183] Next, the second connection electrode CE**2** is disposed on the second planarization layer **149**. The second connection electrodes CE**2** extends from the first plate pattern **121** to the first line pattern **122** to be electrically connected to the first p-type electrode **155** of the first light emitting diode **150**. At this time, at least a part of the second connection electrode CE**2** is disposed in the first groove **149***a* to be in contact with the first reflective layer RL**1**.

[0184] Accordingly, in a display device **100** according to still another example embodiment of the present disclosure, the first light emitting diode **150** of the first sub pixel SP**1** and the light conversion layer CCL can be disposed on the first line pattern **122**. The first light emitting diode **150** and the light conversion layer CCL are disposed on the first line pattern **122** to display red light. The first line pattern **122** extends long in the first direction D**1** or the second direction D**2** and the light conversion layer CCL having a long length can be more easily formed on the first line pattern **122**.

[0185] The example embodiments of the present disclosure can also be described as follows:

[0186] According to an aspect of the present disclosure, a display device includes a lower substrate which includes a plurality of rigid areas disposed to be spaced apart from each other and a malleable area enclosing the plurality of rigid areas, a plurality of first plate patterns disposed in the plurality of rigid areas of the lower substrate, and a plurality of first sub pixels which is partially disposed on the plurality of first plate patterns, and each of the plurality of first sub pixels includes a first light emitting diode, a light conversion layer facing one side surface of the first light emitting diode, and a first reflective layer facing an opposite surface of one side surface of the first light emitting diode.

[0187] The first reflective layer, the first light emitting diode, and the light conversion layer can be disposed on one line and the first light emitting diode can be disposed between the light conversion layer and the first reflective layer.

[0188] The first light emitting diode can include a first emission layer, and one pair of electrodes disposed on and below the first emission layer, and an electrode disposed on the first light emitting layer, between the one pair of electrodes, can be an opaque electrode.

[0189] The display device can further include a first planarization layer disposed below the first light emitting diode, and a second planarization layer disposed on the first planarization layer and the first light emitting diode, and the second planarization layer can include a first groove which has the first reflective layer disposed therein and is disposed to be spaced apart from the first light emitting diode, and a second groove which has the light conversion layer disposed therein.

[0190] The display device can further include a second reflective layer disposed between the second groove and the light conversion layer, and the second reflective layer can be disposed in a remaining part, among a plurality of inner surfaces of the second groove, excluding an inner surface of the second groove facing the first light emitting diode.

[0191] The first reflective layer, the first light emitting diode, and the light conversion layer of each of the plurality of first sub pixels can be disposed on the plurality of first plate patterns.

[0192] Each of the plurality of first plate patterns can include a protrusion protruding to the malleable area and at least a part of each of the plurality of first sub pixels can be disposed on the protrusion.

[0193] The first light emitting diode and the first reflective layer can be disposed on the plurality of first plate patterns and the light conversion layer can be disposed on the protrusion.

[0194] The first planarization layer and the second planarization layer can be disposed to extend from the plurality of first plate patterns to the protrusion.

[0195] The display device can further include a plurality of first line patterns disposed between the plurality of first plate patterns in the malleable area, and at least a part of each of the plurality of first sub pixels can be disposed on the plurality of first line patterns.

[0196] The first light emitting diode and the first reflective layer can be disposed on the plurality of first plate patterns and the light conversion layer can be disposed on the plurality of first line patterns.

[0197] The first planarization layer and the second planarization layer can be disposed to extend from the plurality of first plate patterns to a partial area of the plurality of first line patterns which overlaps the light conversion layer.

[0198] The first light emitting diode, the first reflective layer, and the light conversion layer can be disposed on the plurality of first line patterns.

[0199] The first planarization layer and the second planarization layer can be disposed to extend from the plurality of first plate patterns to a partial area of the plurality of first line patterns which overlaps the first light emitting diode, the first reflective layer, and the light conversion layer.

[0200] Although the example embodiments of the present disclosure have been described in detail with reference to the accompanying drawings, the present disclosure is not limited thereto and can be embodied in many different forms without departing from the technical concept of the present disclosure. Therefore, the example embodiments of the present disclosure are provided for illustrative purposes only but not intended to limit the technical concept of the present disclosure. The scope of the technical concept of the present disclosure is not limited thereto. Therefore, it should be understood that the above-described example embodiments are illustrative in all aspects and do not limit the present disclosure. All the technical concepts in the equivalent scope of the present disclosure should be construed as falling within the scope of the present disclosure.

What is claimed is:

1. A display device, comprising:

a lower substrate including a plurality of rigid areas disposed to be spaced apart from each other and a malleable area enclosing the plurality of rigid areas;

a plurality of first plate patterns disposed in the plurality of rigid areas of the lower substrate; and

a plurality of first sub pixels partially disposed on the plurality of first plate patterns,

wherein each of the plurality of first sub pixels includes:

a first light emitting diode;

a light conversion layer facing one side surface of the first light emitting diode; and

a first reflective layer facing an opposite surface of one side surface of the first light emitting diode.

2. The display device according to claim **1**, wherein the first reflective layer, the first light emitting diode, and the light conversion layer are disposed on one line, and the first light emitting diode is disposed between the light conversion layer and the first reflective layer.

3. The display device according to claim **1**, wherein the first light emitting diode includes:

a first emission layer; and

one pair of electrodes disposed on and below the first emission layer, and

wherein an electrode disposed on the first light emitting layer, between the one pair of electrodes, is an opaque electrode.

4. The display device according to claim **1**, further comprising:

a first planarization layer disposed below the first light emitting diode; and

a second planarization layer disposed on the first planarization layer and the first light emitting diode, and

wherein the second planarization layer includes:

a first groove having the first reflective layer disposed therein and disposed to be spaced apart from the first light emitting diode; and

a second groove having the light conversion layer disposed therein.

5. The display device according to claim **4**, further comprising:

a second reflective layer disposed between the second groove and the light conversion layer,

wherein the second reflective layer is disposed in a remaining part, among a plurality of inner surfaces of the second groove, excluding an inner surface of the second groove facing the first light emitting diode.

6. The display device according to claim **4**, wherein the first reflective layer, the first light emitting diode, and the light conversion layer of each of the plurality of first sub pixels are disposed on the plurality of first plate patterns.

7. The display device according to claim **4**, wherein each of the plurality of first plate patterns includes a protrusion protruding to the malleable area, and

wherein at least a part of each of the plurality of first sub pixels is disposed on the protrusion.

8. The display device according to claim **7**, wherein the first light emitting diode and the first reflective layer are disposed on the plurality of first plate patterns, and the light conversion layer is disposed on the protrusion.

9. The display device according to claim **8**, wherein the first planarization layer and the second planarization layer are disposed to extend from the plurality of first plate patterns to the protrusion.

10. The display device according to claim **4**, further comprising:

a plurality of first line patterns disposed between the plurality of first plate patterns in the malleable area,

wherein at least a part of each of the plurality of first sub pixels is disposed on the plurality of first line patterns.

11. The display device according to claim **10**, wherein the first light emitting diode and the first reflective layer are disposed on the plurality of first plate patterns, and the light conversion layer is disposed on the plurality of first line patterns.

12. The display device according to claim **11**, wherein the first planarization layer and the second planarization layer are disposed to extend from the plurality of first plate patterns to a partial area of the plurality of first line patterns which overlaps the light conversion layer.

13. The display device according to claim **10**, wherein the first light emitting diode, the first reflective layer, and the light conversion layer are disposed on the plurality of first line patterns.

14. The display device according to claim **13**, wherein the first planarization layer and the second planarization layer are disposed to extend from the plurality of first plate patterns to a partial area of the plurality of first line patterns which overlaps the first light emitting diode, the first reflective layer, and the light conversion layer.

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